

A Short Guide to Cryogenic Probing & Transport Measurements

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Applications Scientist

Why probing?

Flexible electrical measurement platform enabling:

- Wafer-level characterization
(avoid time and cost of packaging)

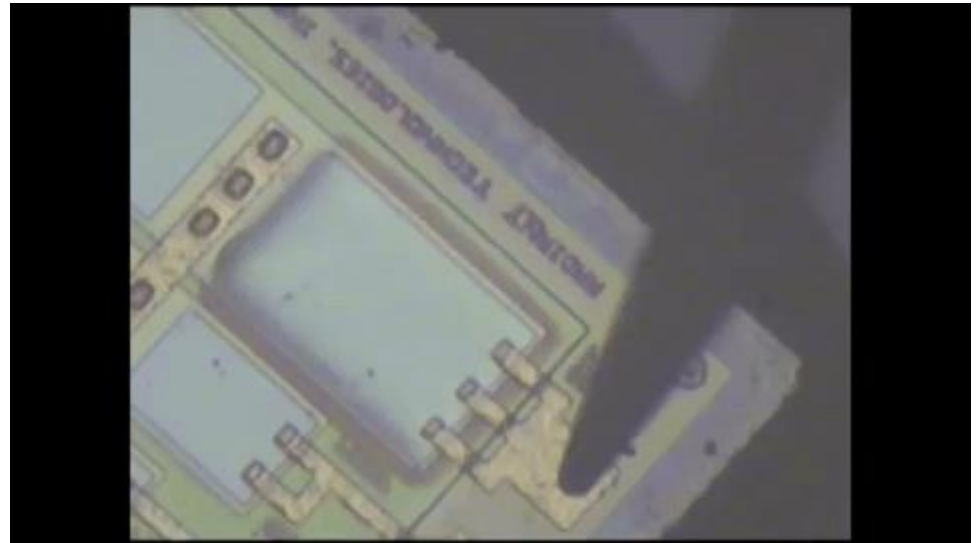
Manual probe stations ideal for research-scale characterization



Why probing?

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(avoid packaging)
- Device visualization



"Rapidly Characterize Ferroelectric Devices over Variable Temperatures"
Lake Shore Application Note, www.lakeshore.com

Why probing?

Flexible electrical measurement platform enabling:

- Wafer-level characterization
(avoid packaging)
- Device visualization
- Environmental control
(atmosphere, temperature, field, light,...)

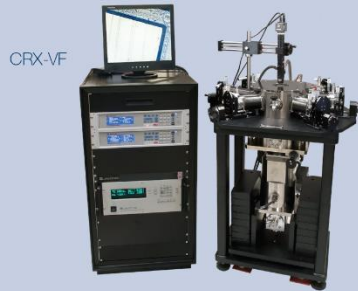
Range of platforms

Cryogen-Free Probe Stations

Horizontal Field



Vertical Field



No Field



Cryogenic Probe Stations



Anatomy of a cryogenic probe station

Sample stage


Sample stage (4.3 K)

Anatomy of a cryogenic probe station

Sample stage

Sample stage (4.3 K)

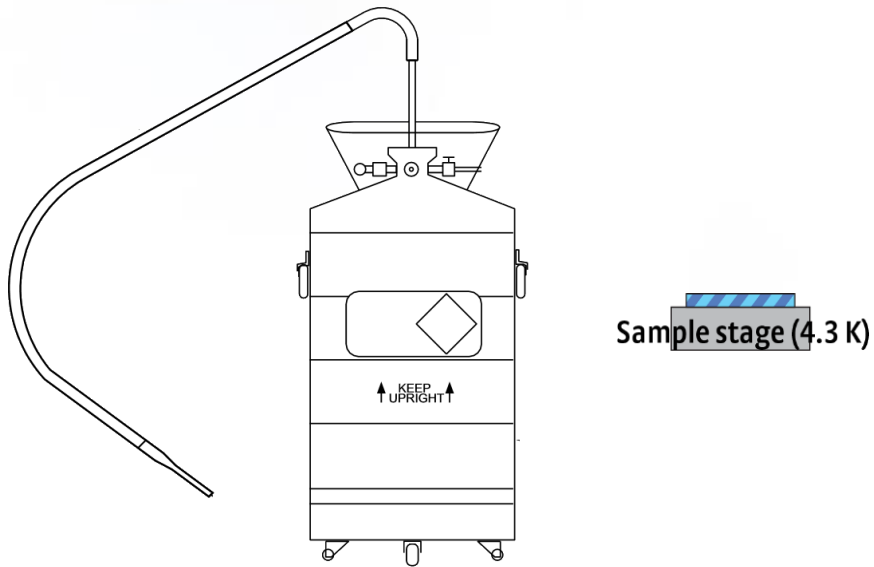
Gifford-McMahon (GM) cooler

- No liquid cryogenics
- "Closed-cycle" system



Anatomy of a cryogenic probe station

Sample stage



Liquid helium or nitrogen

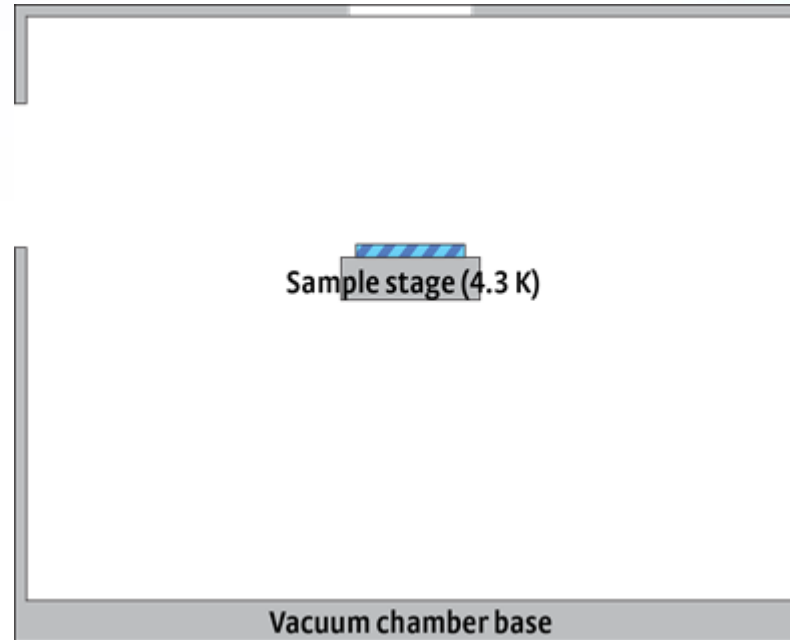
- "Wet" system
- Often lowest vibrations
- Faster cycle times

Anatomy of a cryogenic probe station

Vacuum chamber

Prevents gas adsorbates
freezing to surface of wafer

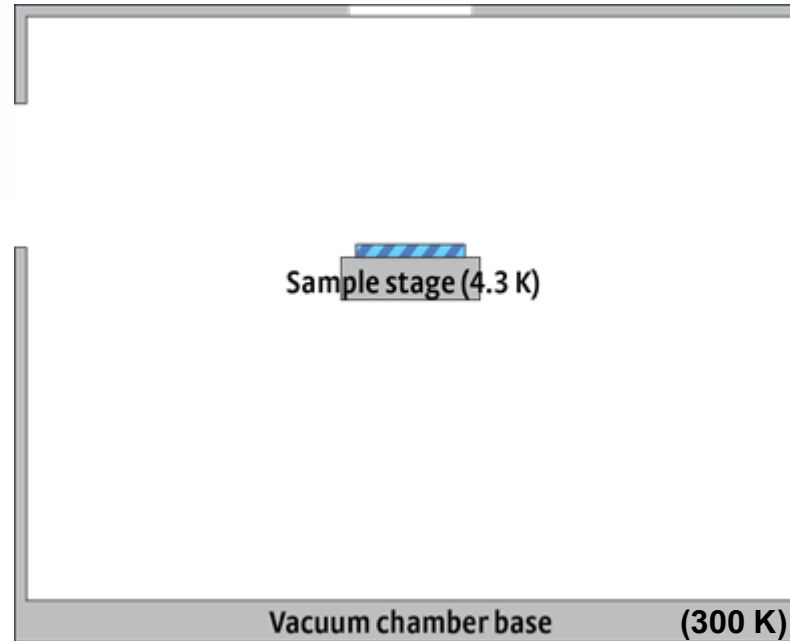
- Frozen air is a great insulator
- Poor vacuum at room temperature can lead to poor electrical contact at cold temperatures



Anatomy of a cryogenic probe station

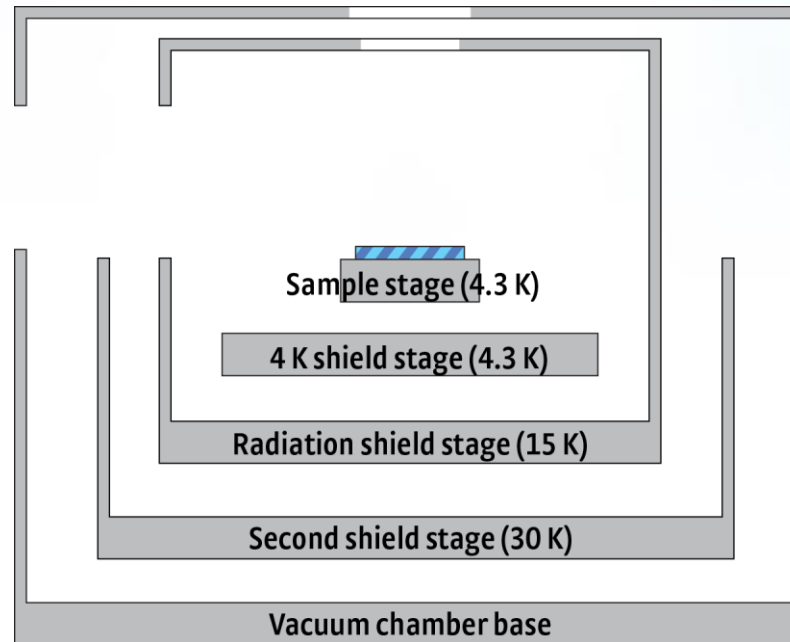
Thermal radiation

$$\dot{Q} \propto T_{hot}^4 - T_{cold}^4$$



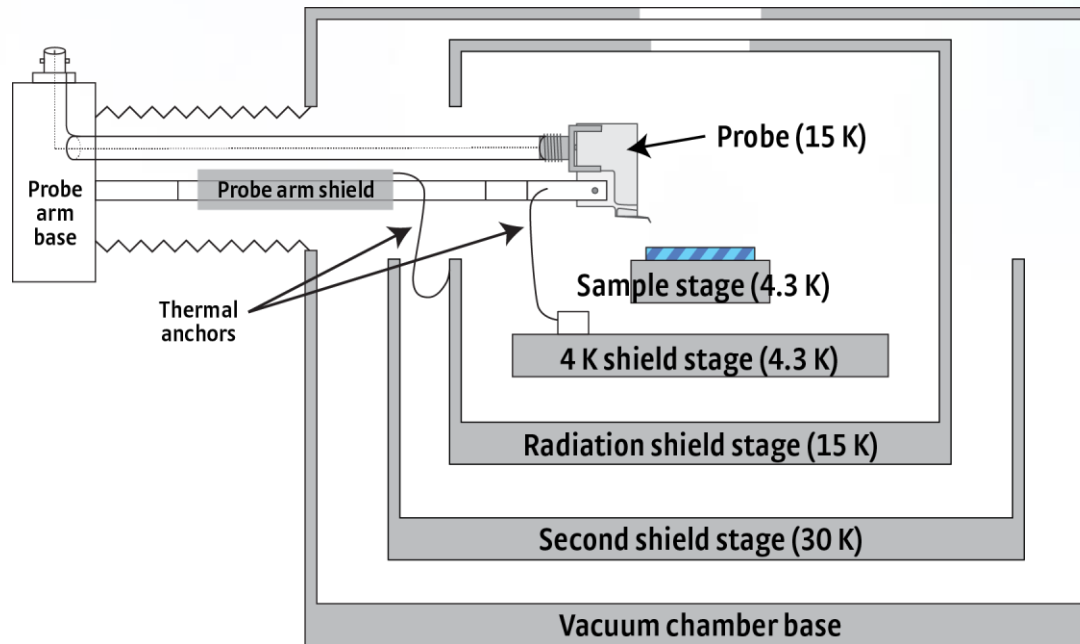
Anatomy of a cryogenic probe station

Radiation shield



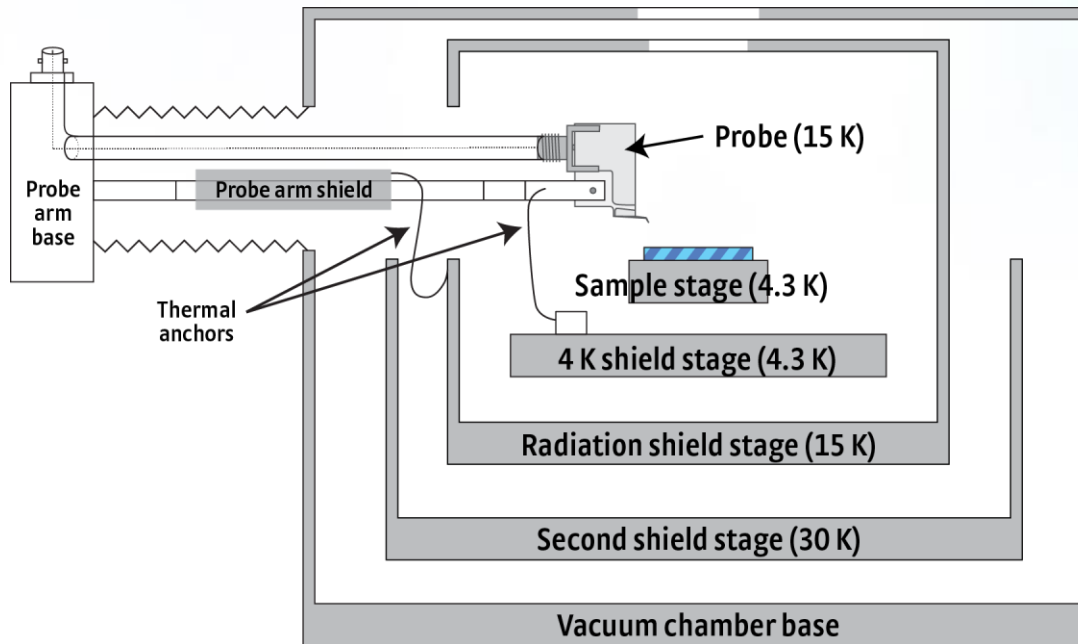
Anatomy of a cryogenic probe station

Probe arm



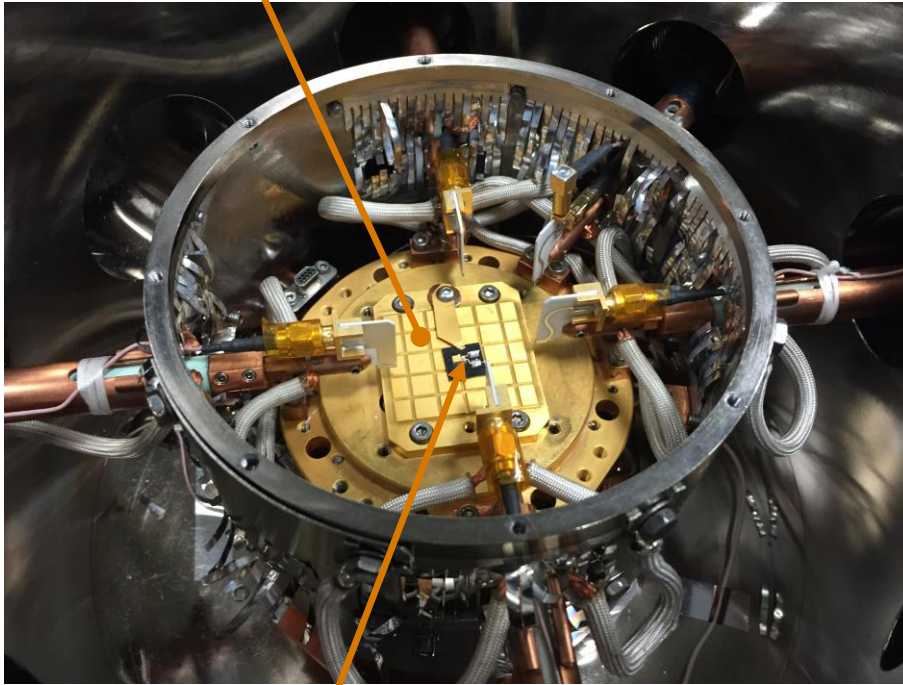
Anatomy of a cryogenic probe station

Probe arm design to limit thermal conduction

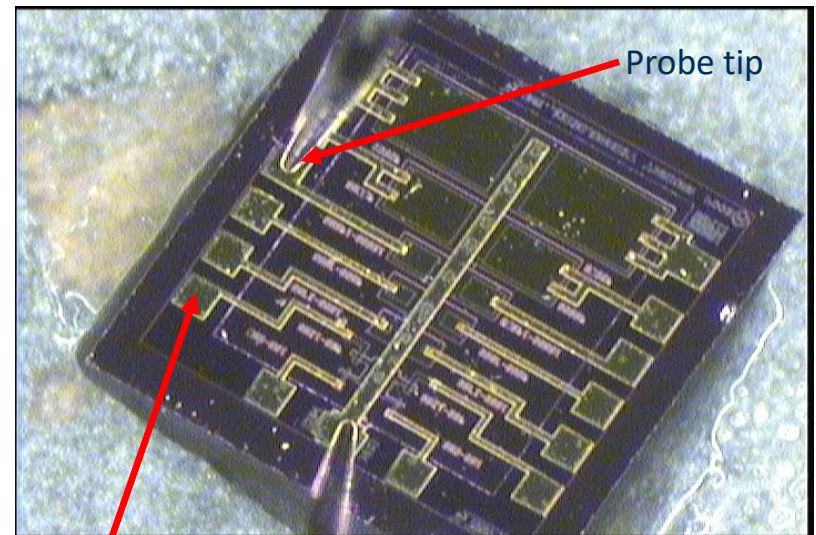
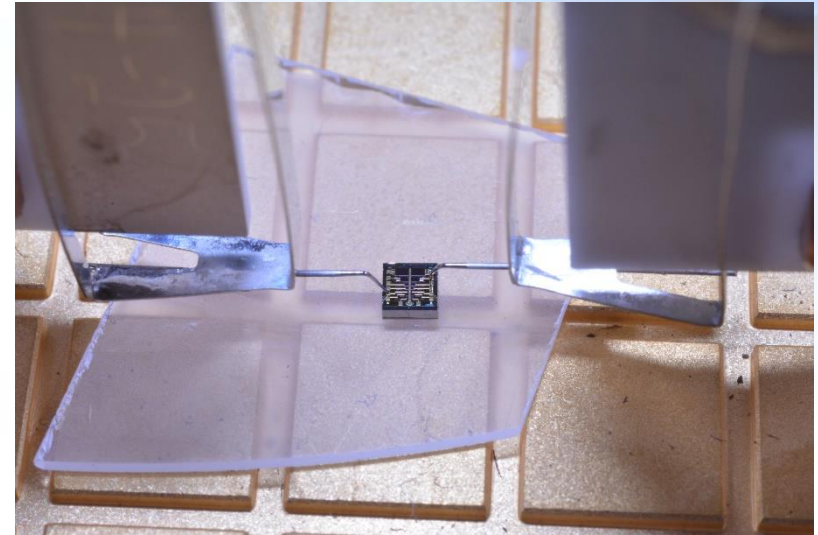


Cryogenic probe stations in a nutshell

The stage gets really cold, or fairly hot
1.3 K to 675 K (-457 °F to 750 °F)

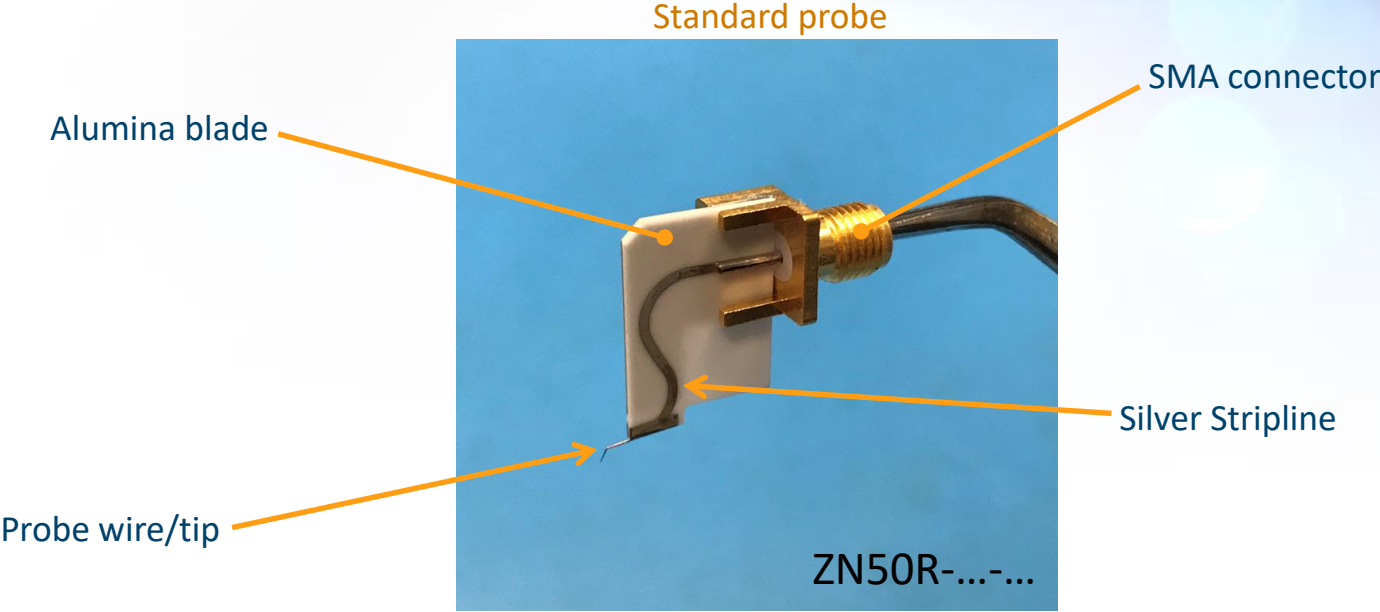


Need to make electrical contacts to a device on the stage

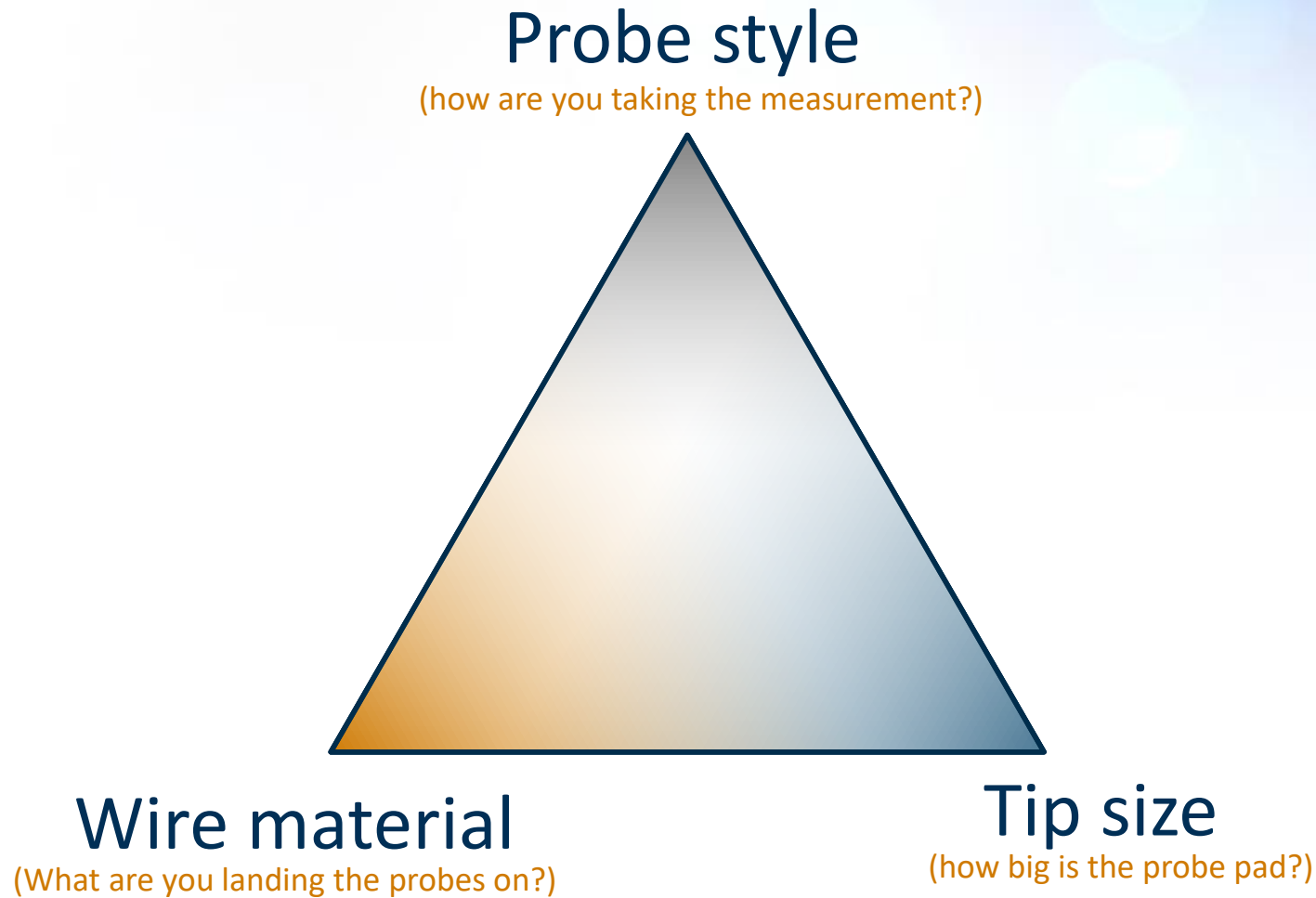


Probe pad

The ZN50 probe

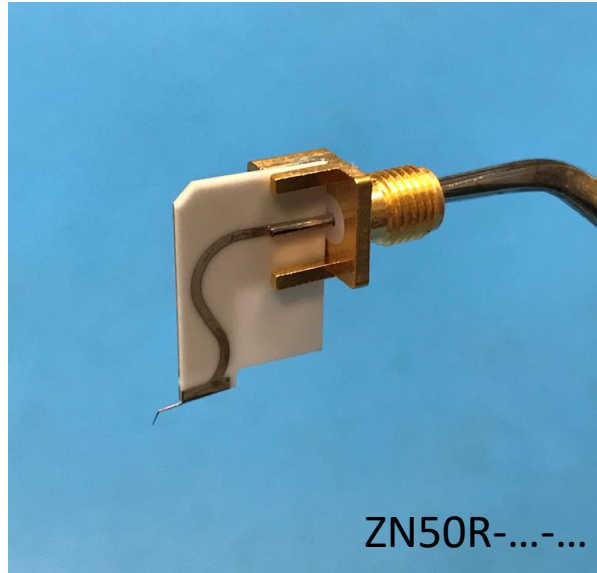


Tailoring the probe to the application



Probe style

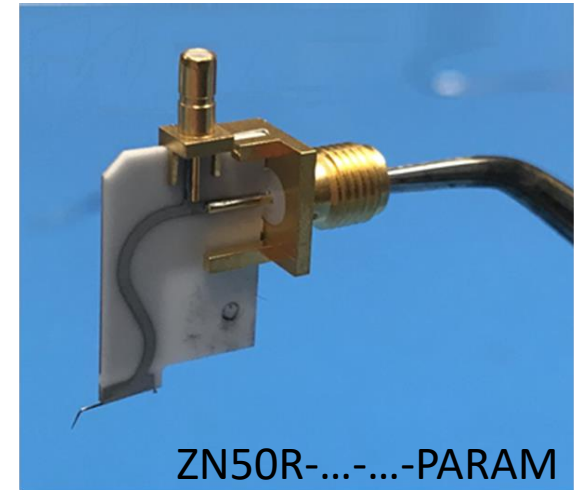
Standard probe



Continuous variable temperature probe



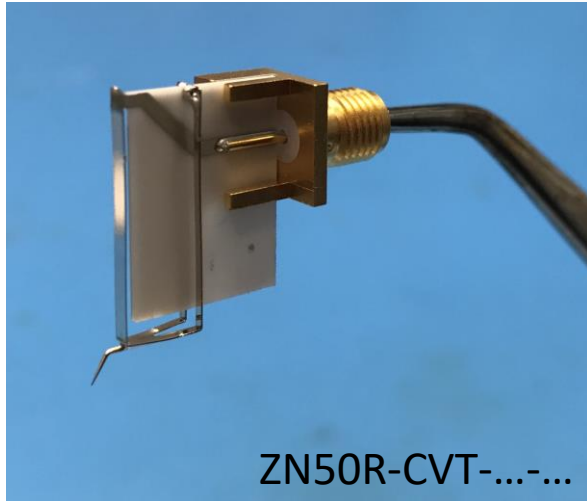
Parametric (or dual connector) probe



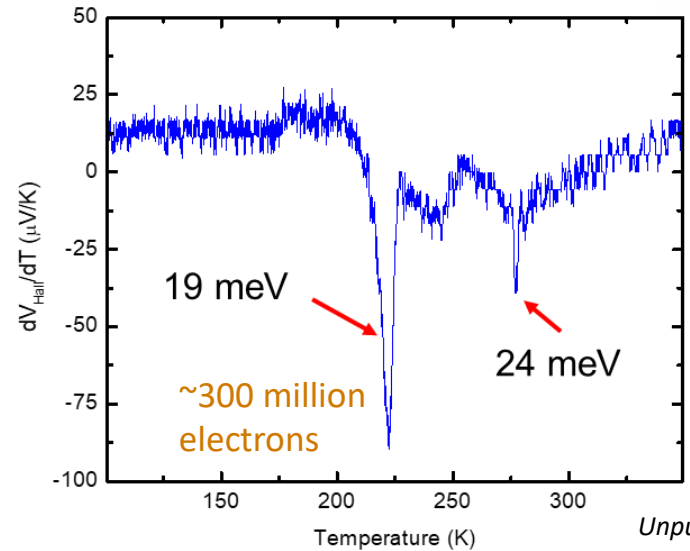
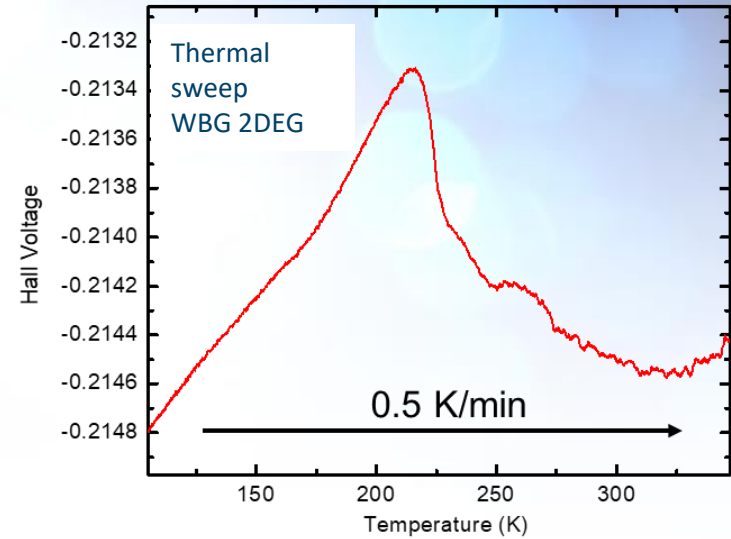
Probe style: CVT

Continuous Variable Temperature Probe

Continuous electrical contact
across temperature



Lake Shore probe station catalog, www.lakeshore.com

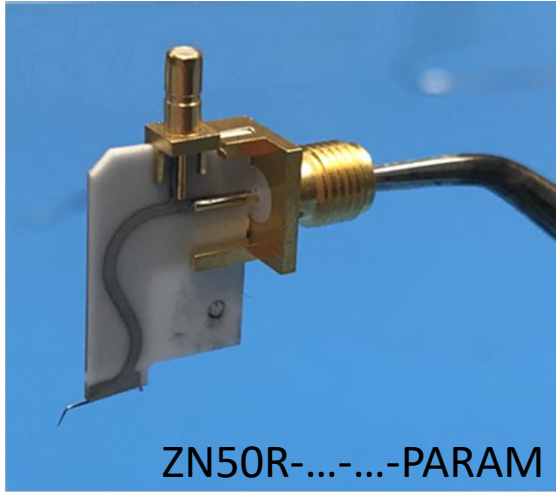


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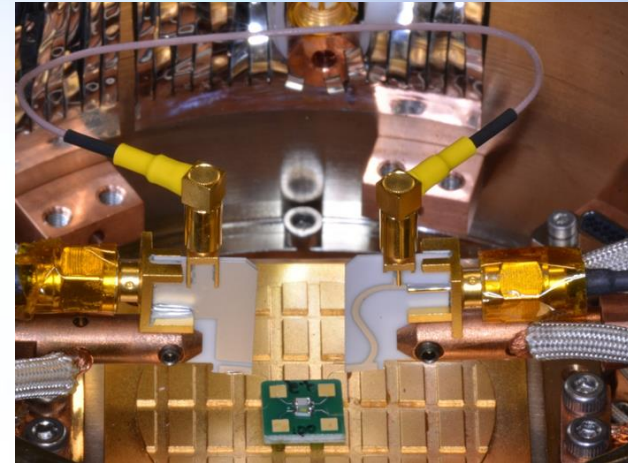


Probe style: parametric (C-V measurements)

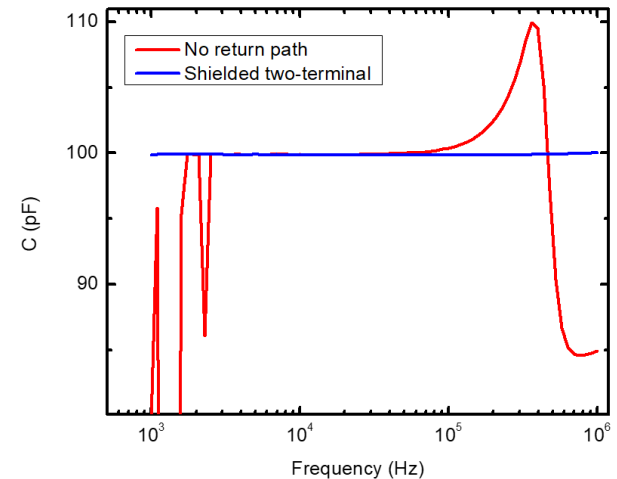
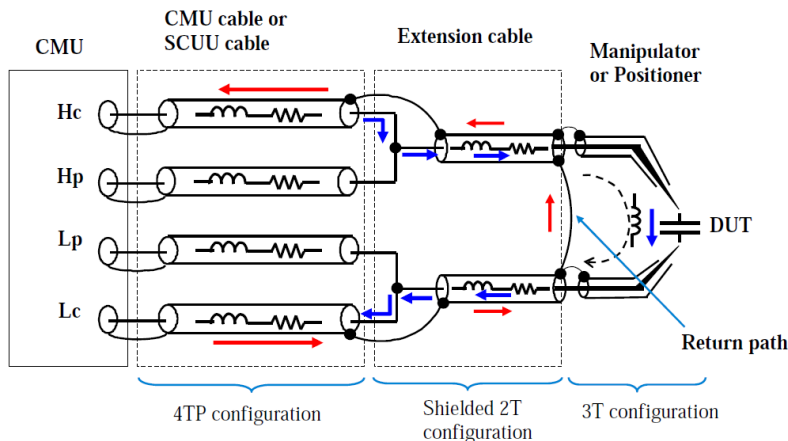
Parametric (or dual connector) probe



Ground and signal routing in proximity to the DUT



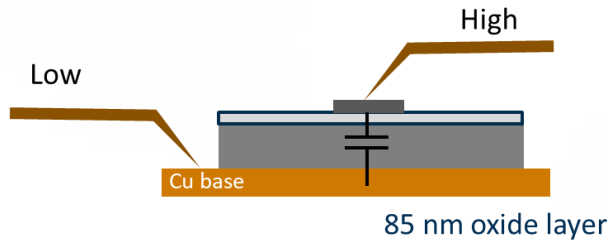
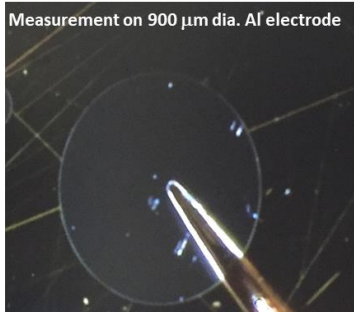
- “S-2T” configuration reduces stray inductance in probe arm cabling – improves reliability of C-V measurement



“Variable-Temperature, Wafer-Level Capacitance Measurements”
Lake Shore Application Note, www.lakeshore.com

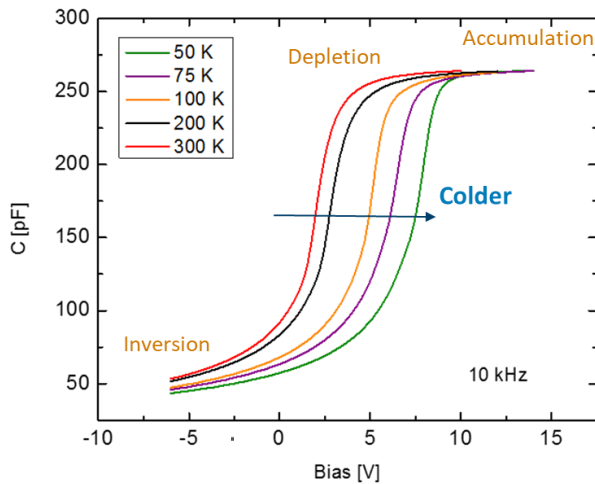
Temperature-dependent C-V results

SiC MOS structure

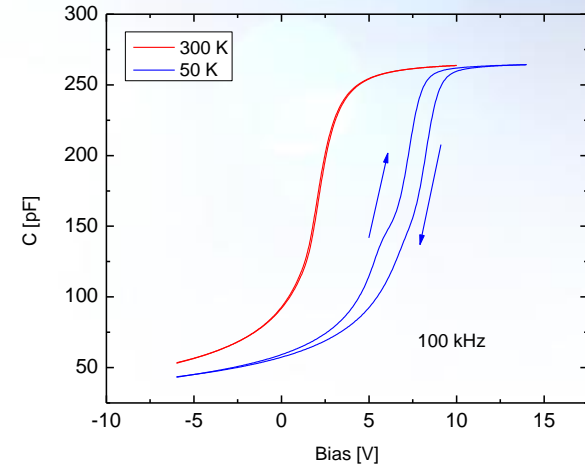


Unpublished

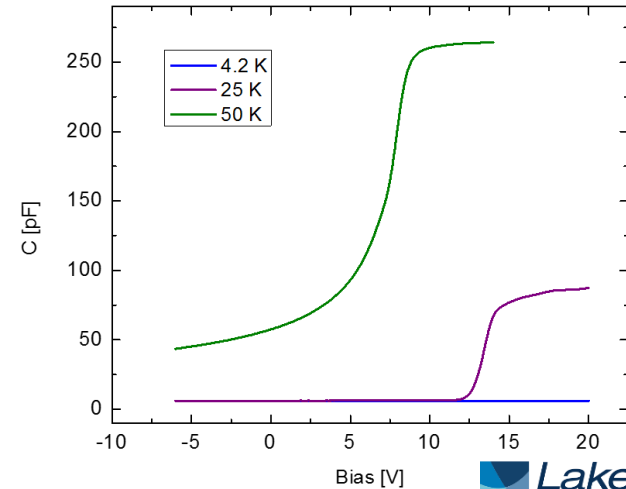
Drastic shift in C-V characteristic as temperature is lowered



“Clockwise” hysteresis indicative of surface-state traps

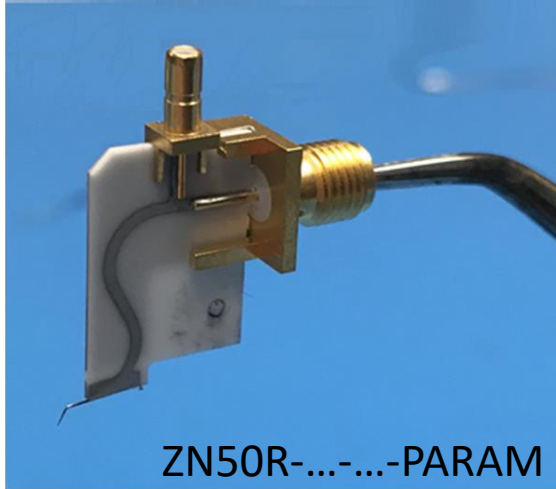


Below 50 K you start seeing carrier freeze out effects



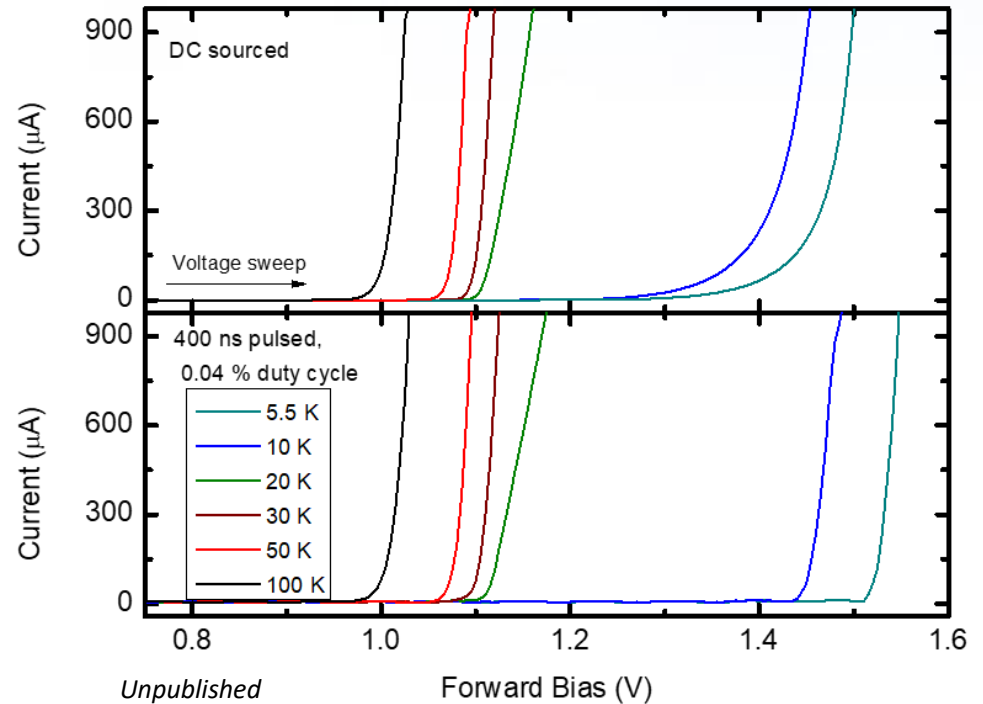
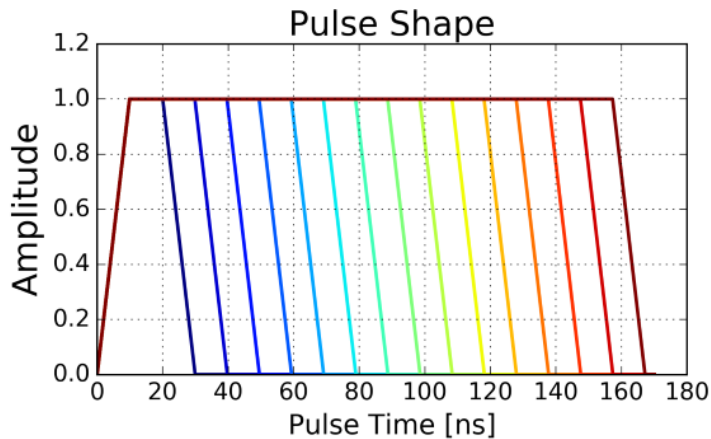
Probe style: parametric (pulsed measurements)

Parametric (or dual connector) probe



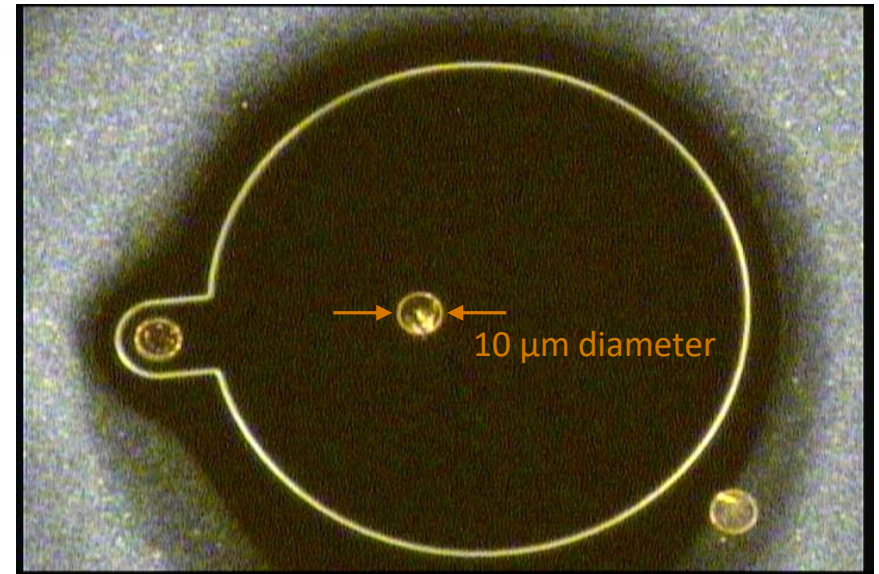
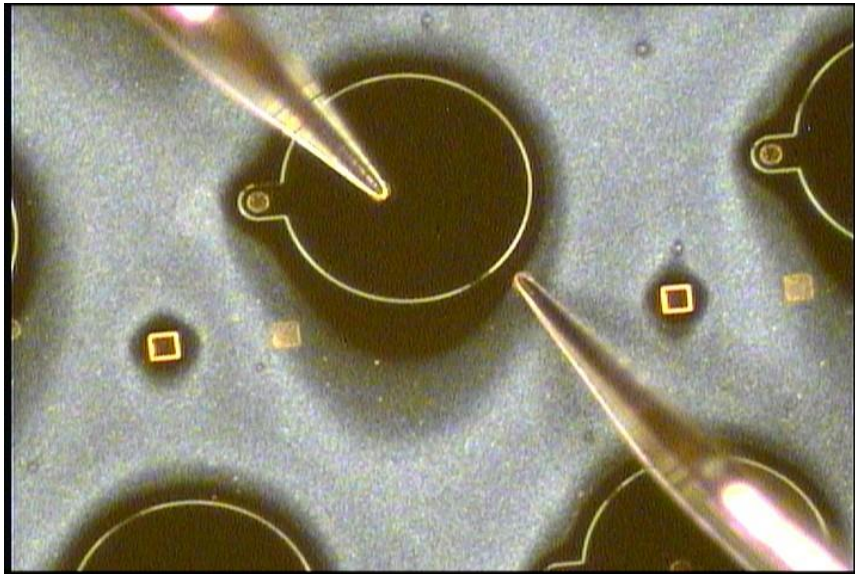
Ground and signal routing
in proximity to the DUT

Cryo temperatures: Duty cycle and pulse duration



Probe size

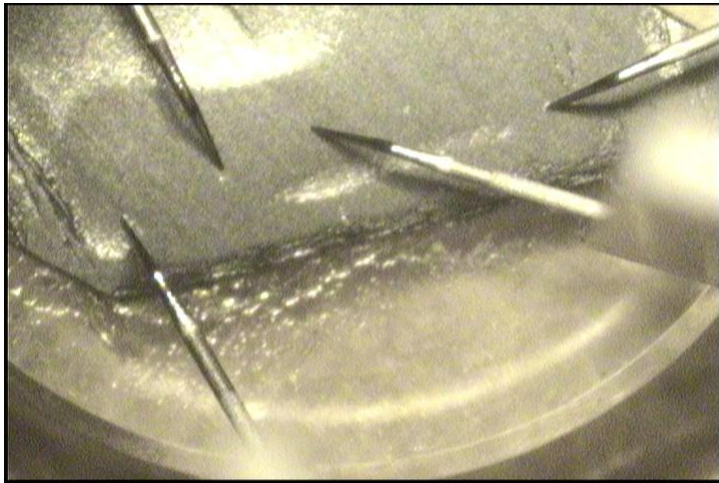
- Largely, probe wire is 250 micron in diameter and is tapered to a point
- Tip size is tailored to the pad size
- Probe point can be as large as 100 μm radius and as small as 3 μm radius



Probe material

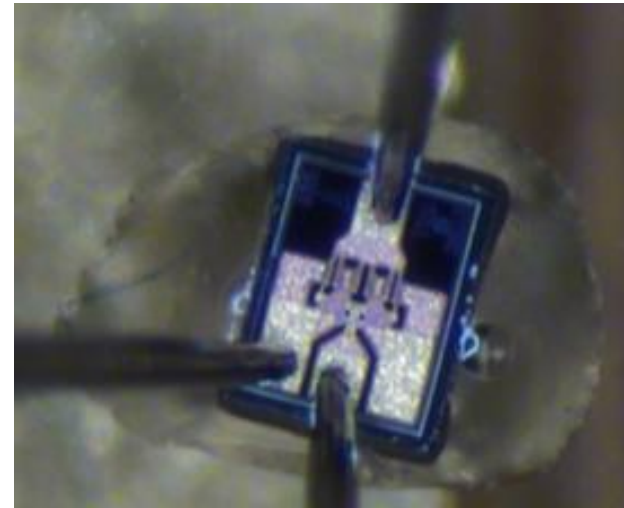
Material	Pro(s)	Con(s)
Beryllium copper (BeCu)	Low contact resistance, easy to clean	Quickly oxides, wire easily deforms
Tungsten (W)	Punctures oxides, robust	Difficult to clean, punctures wrong oxide
Paliney 7 (P7)	High corrosion resistance	Wire easily deforms
Gold-coated tungsten (Au)	Robust + low contact resistance to Au	Au layer wears

Tungsten tips on niobium sheet



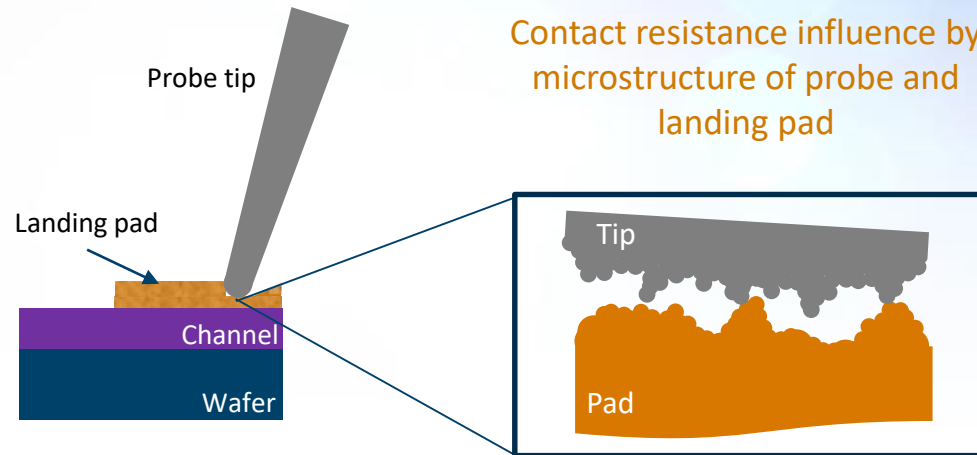
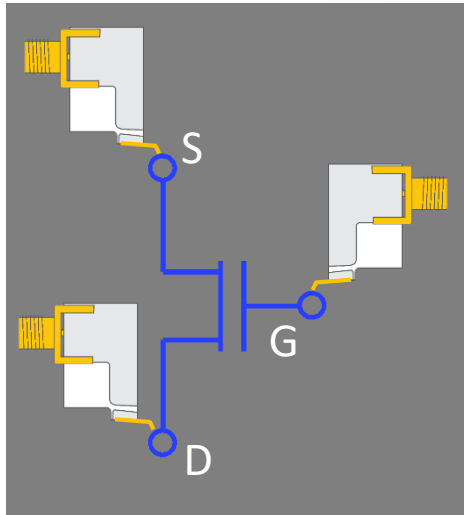
Moh hardness of Nb oxides similar to quartz (~7)

BeCu tips on gold transistor contacts

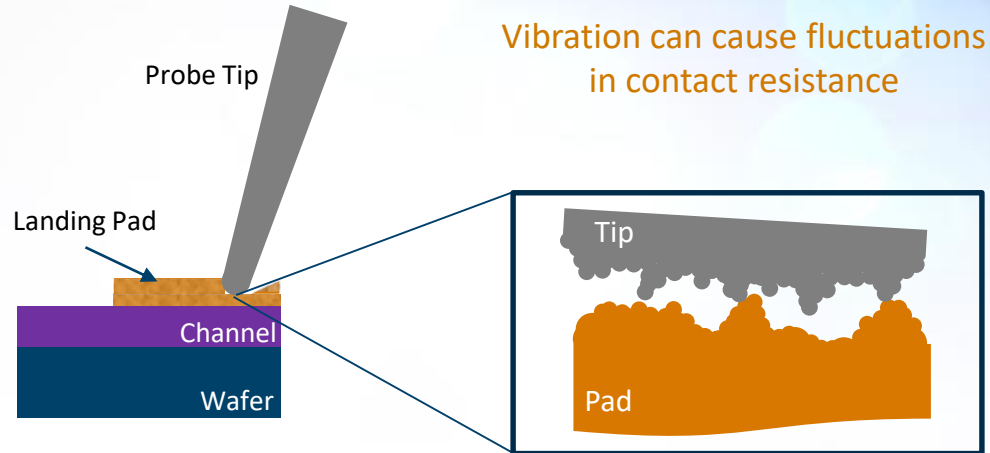
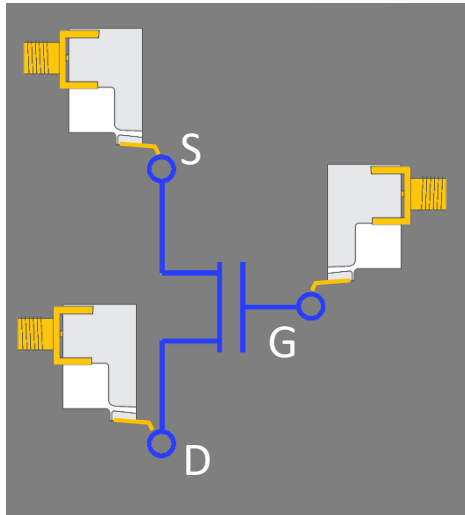


Moh hardness of Au around 2.5 to 3

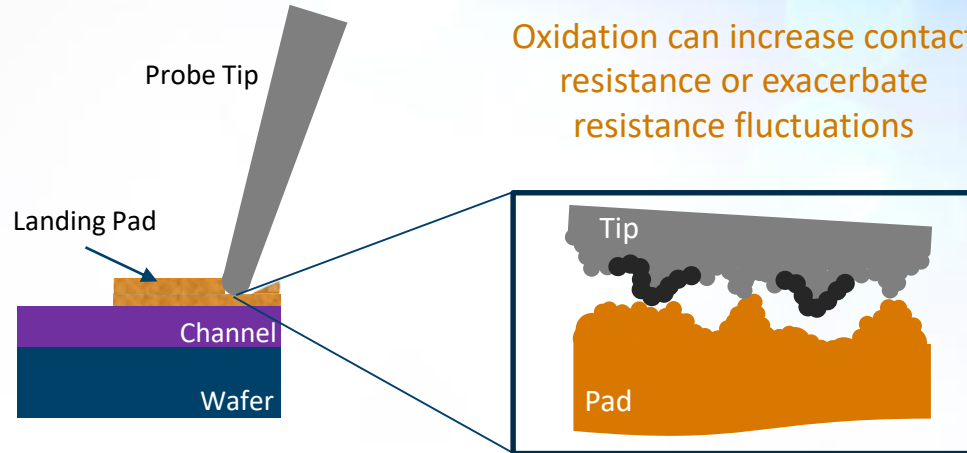
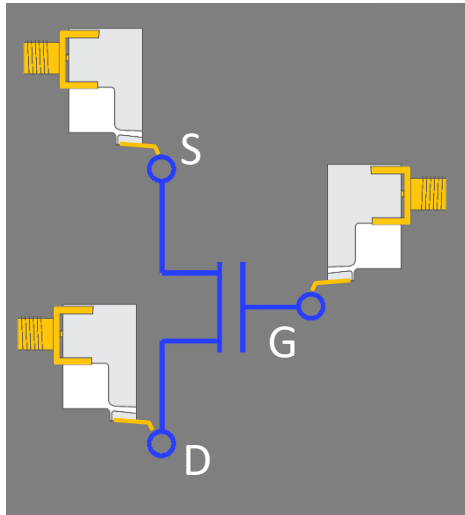
Contact resistance



Contact resistance

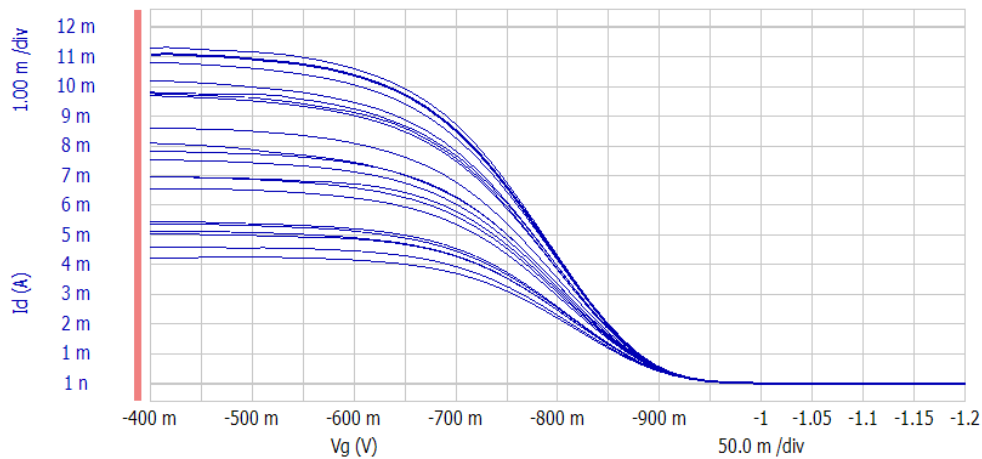


Contact resistance



Oxidation can increase contact resistance or exacerbate resistance fluctuations

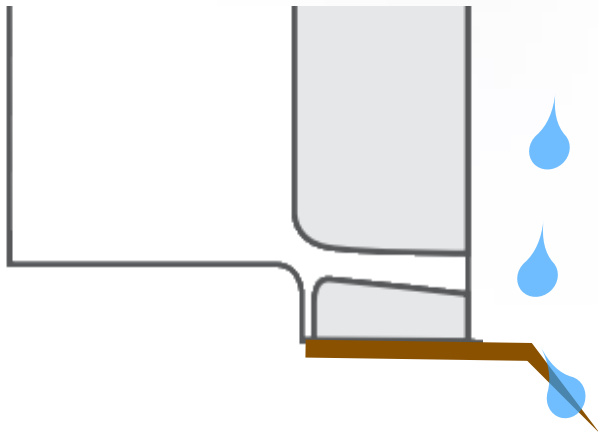
Repeated Transfer curves at 77 K



Consistency and repeatability checks are a valuable tool to evaluate contact resistance.

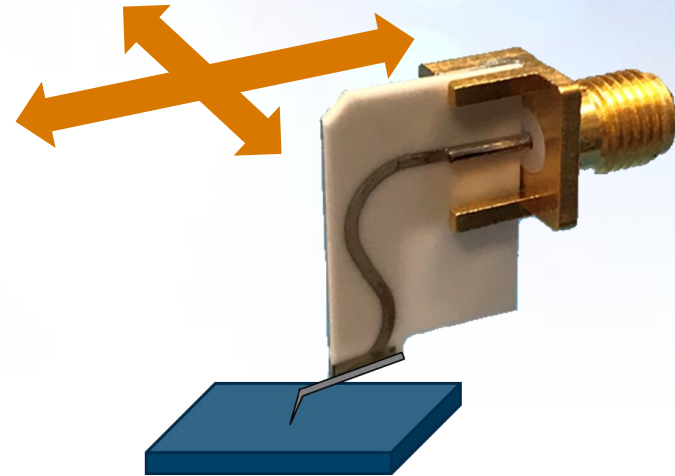
Cleaning dirty probes

BeCu/Au/P7 probe wire



- Organic contaminants removed with solvent
- BeCu oxidation removed with Tarnix, rinse after (see manual)
- Especially for smaller radius tips, apply liquid to knee of probe and let droplets run down probe wire

W probe wire



- Organic contaminants removed with solvent
- Don't recommend corrosives to remove oxidation
- Mechanical removal
 - Tip paper
 - Clean, broken probe blade
 - In a pinch, clean paper with tight grain (Post-Its, surprisingly)

Probe tip tips

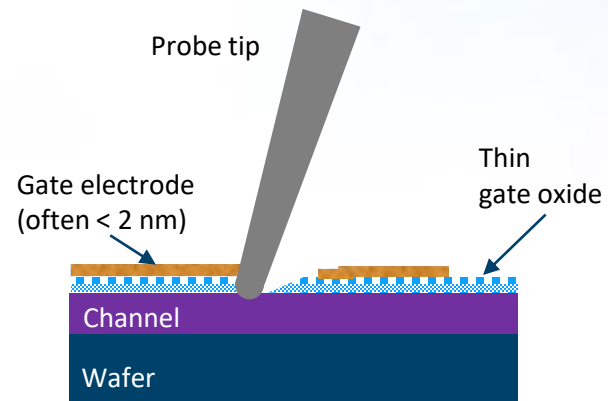
Poor electrical contact with CVT on oxidized probing pads



Consider:

- Standard ZN50 with W probes
- Lateral (left-right) scrubbing of probe pad with CVT probe tip

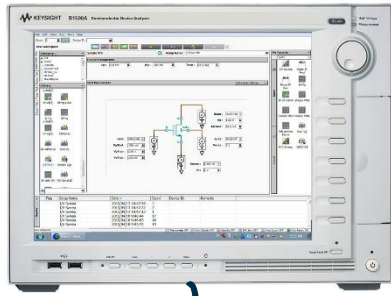
Probe puncture – electrically shorting gate electrode to channel



Consider:

- CVT probes with Au-coated tips
- Different probe material (BeCu or P7)
- Reduce overtravel on landing

The semiconductor analyzer



B1500A/EasyEXPERT
(GPIB interface)

*Automated
temperature
changes*

*Automated
magnetic field
changes*



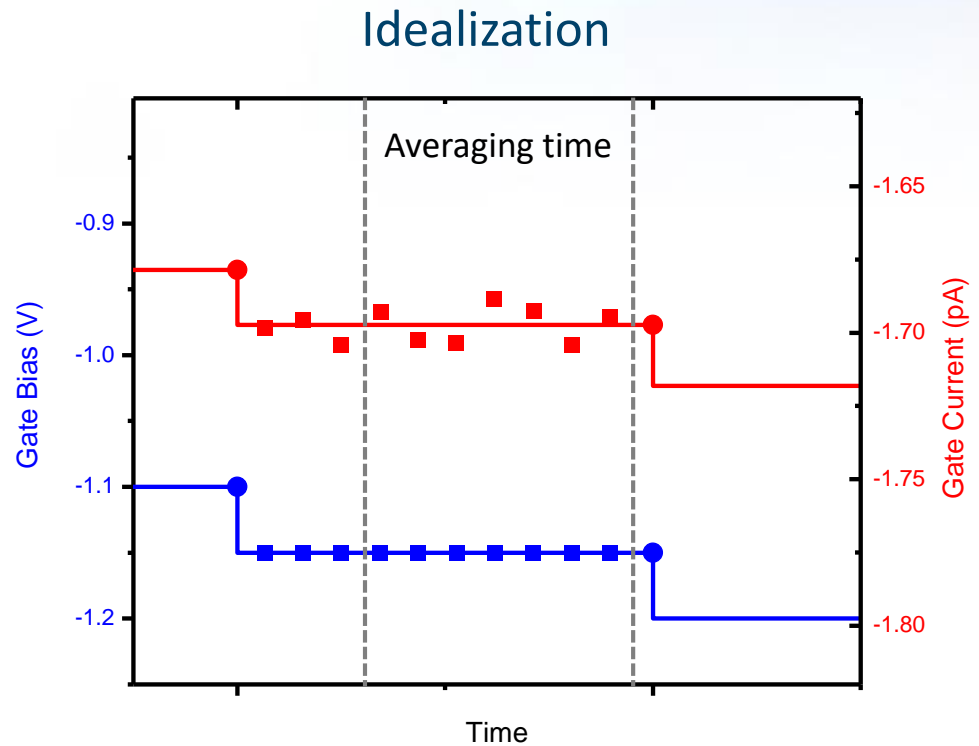
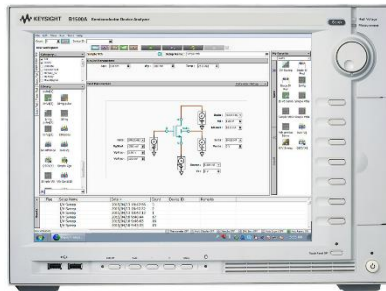
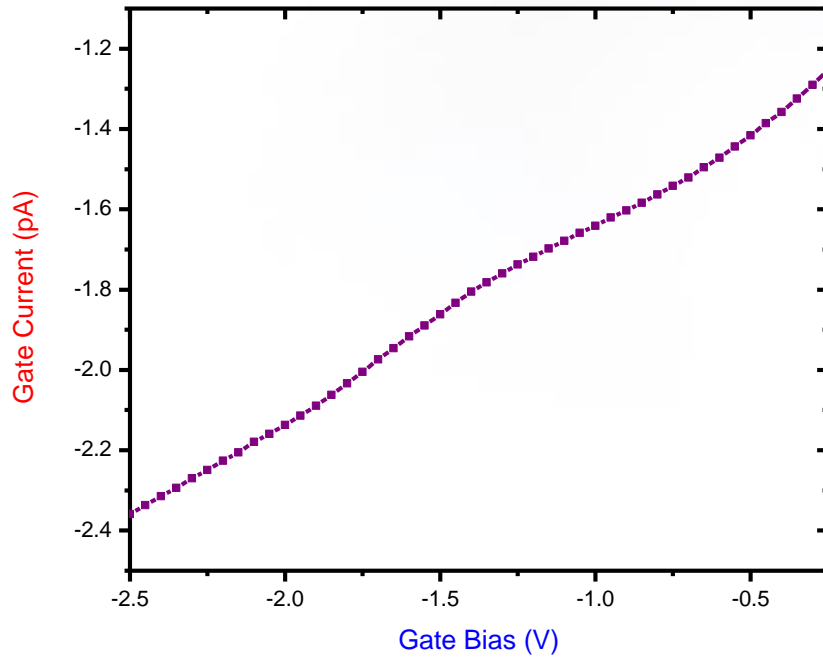
Lake Shore probe station

*Device
measurement*

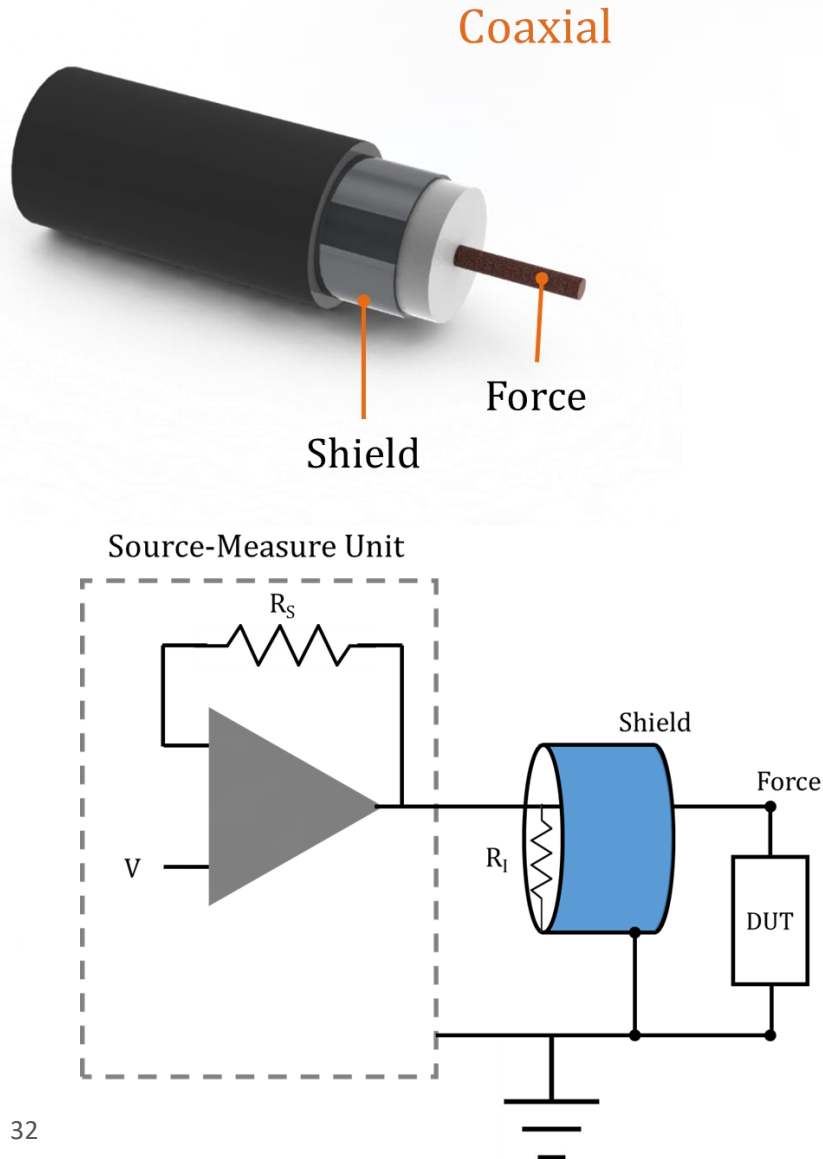


- Lake Shore temperature and mag field controller interfaces with Keysight B1500
- Lake Shore temperature controller interfaces with Keithley 4200

Low current transport (I-V) measurements

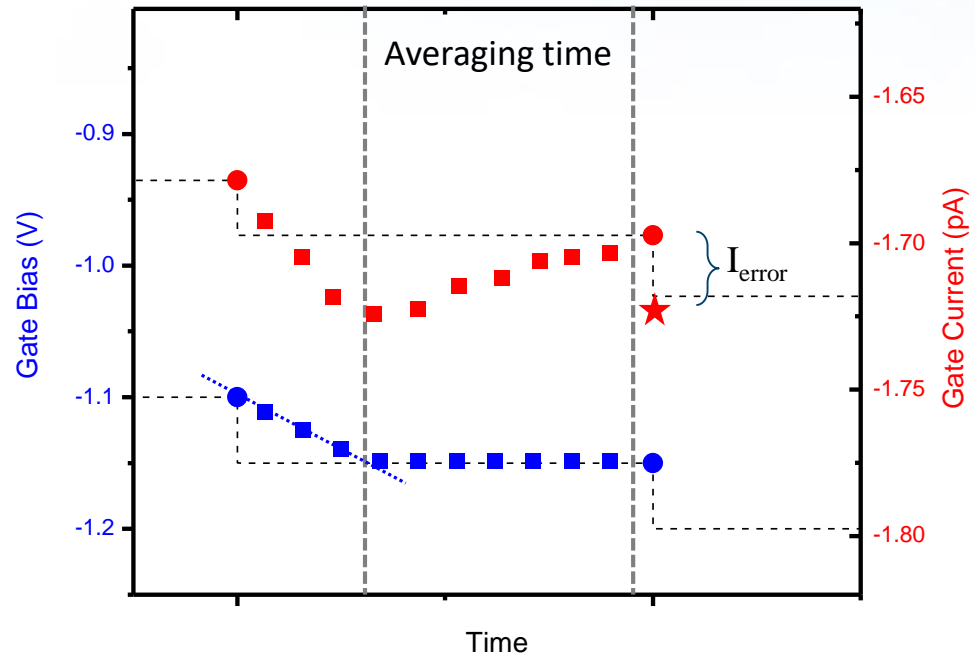


Low current transport (I-V) measurements



Charging current due to cable capacitance

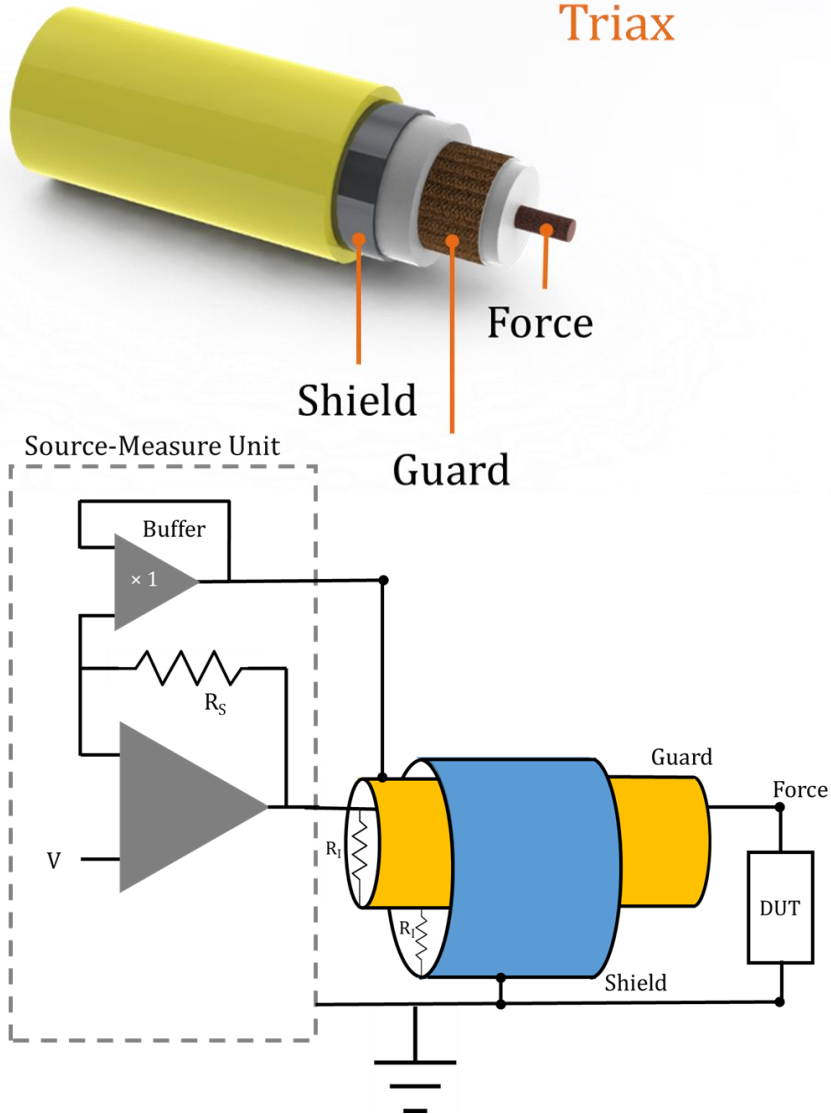
$$I_c = C \frac{dV}{dt}$$



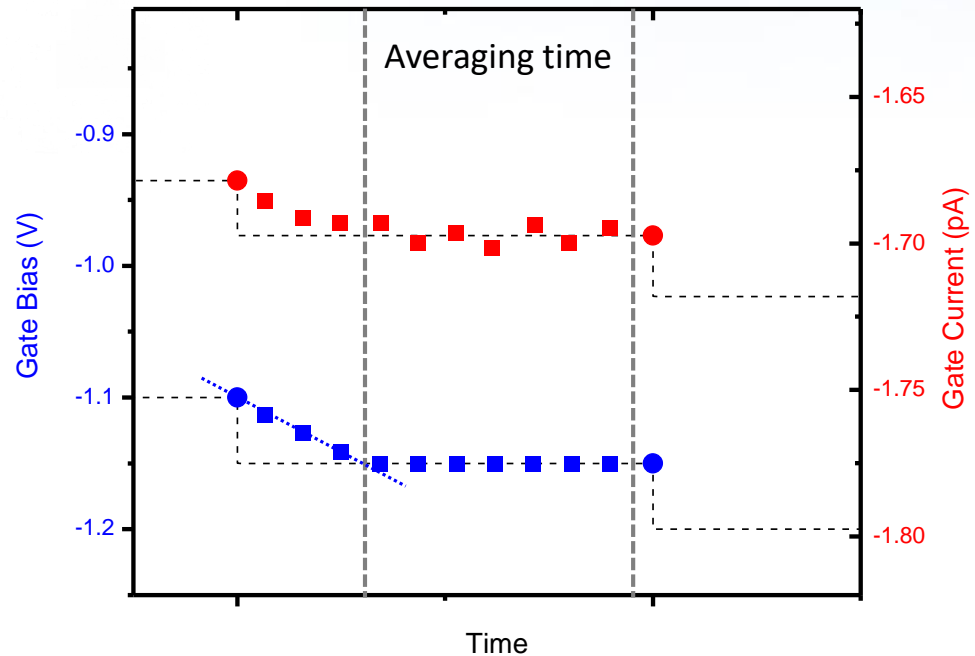
"Considerations for Low Current Measurements in Cryogenic Probe Stations"
Lake Shore Application Note, www.lakeshore.com

Low current transport (I-V) measurements

Triax

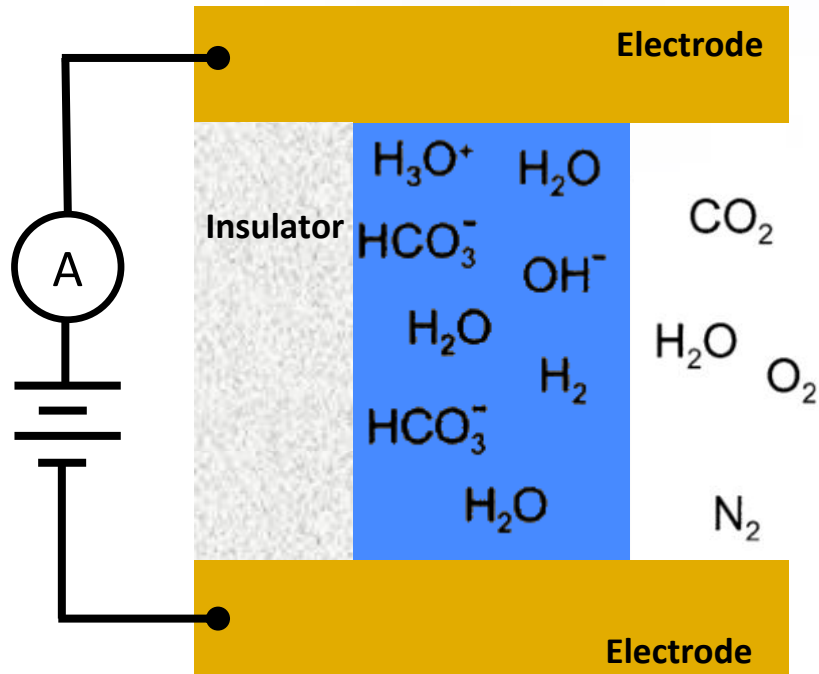


Guard and force at same potential to minimize effect from charging current

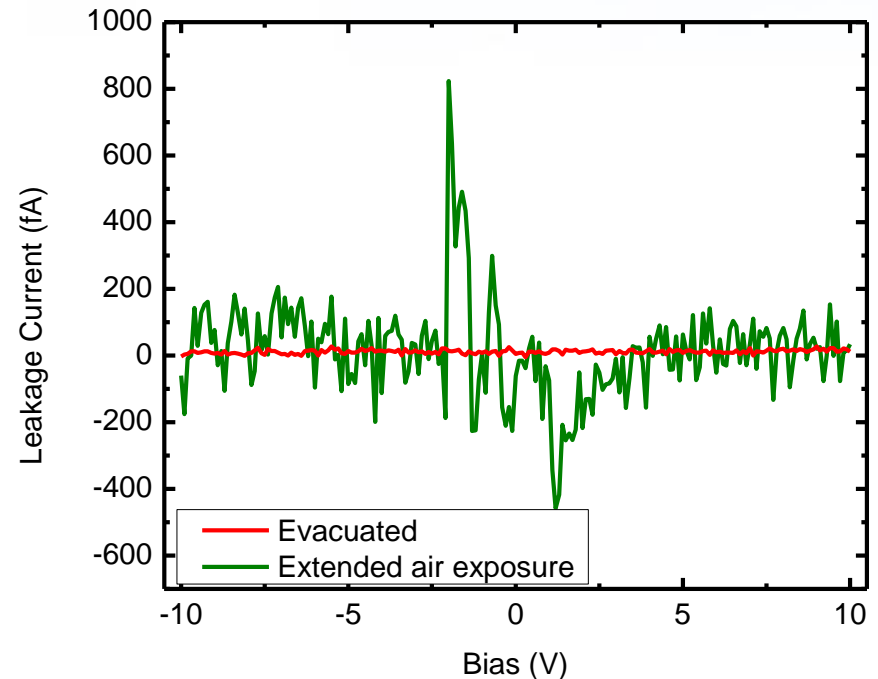


"Considerations for Low Current Measurements in Cryogenic Probe Stations"
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Low current transport (I-V) measurements



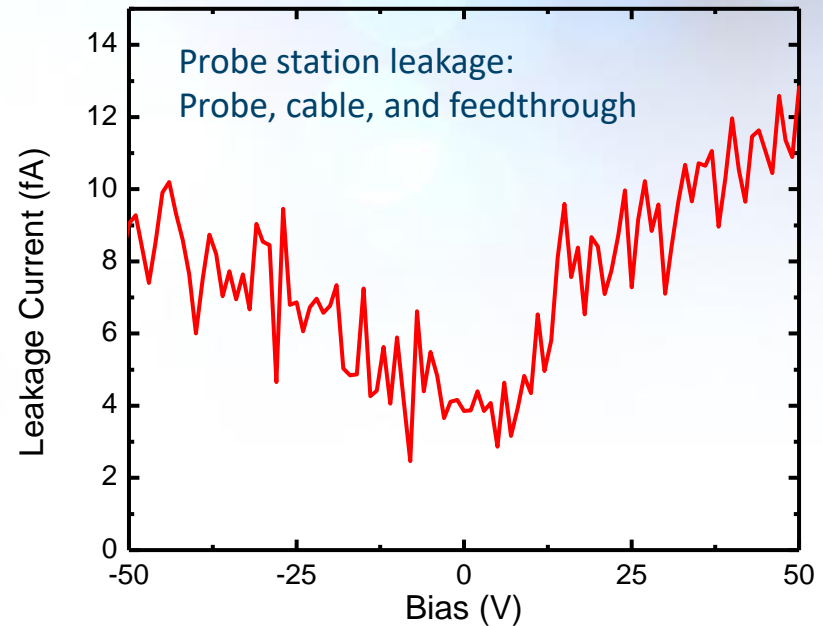
Water vapor absorbed on surfaces can open additional, unintended conduction channels



Evacuate or gas purge your probed measurements

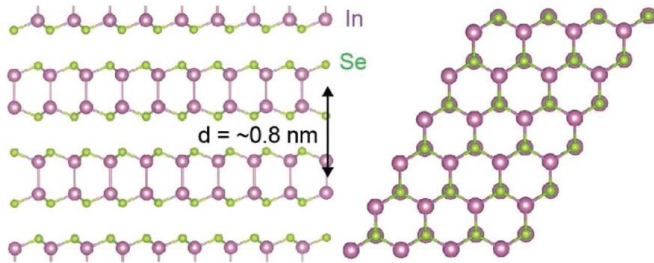
Low current transport (I-V) measurements

- Triaxial configuration for low-current measurements
 - 3-lug, triaxial vacuum feedthrough
 - Guarded measurement from analyzer to the probe
 - Optional triaxial sample stage for backside device contact
- Use high quality triaxial cabling from instrumentation to prober
- Minimize flexing of cabling

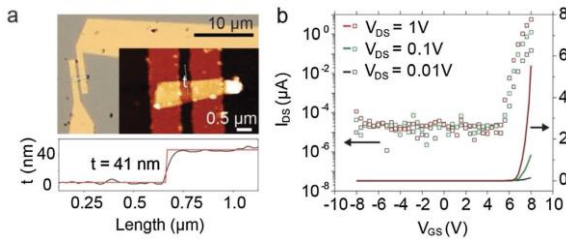


Cryogenic Evacuated transport (I-V) measurements

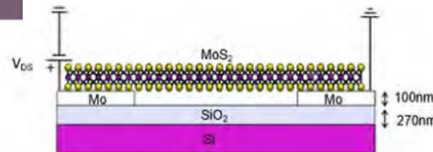
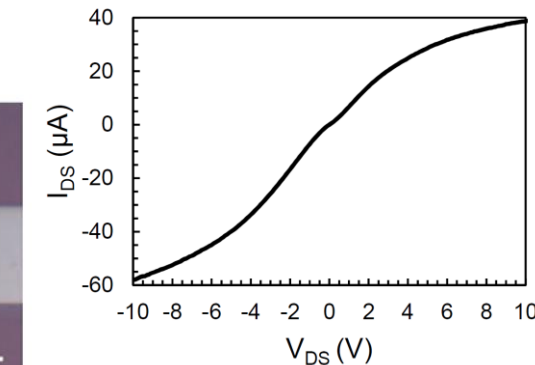
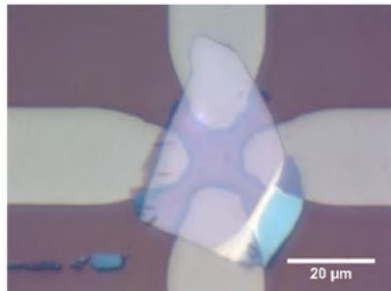
InSe



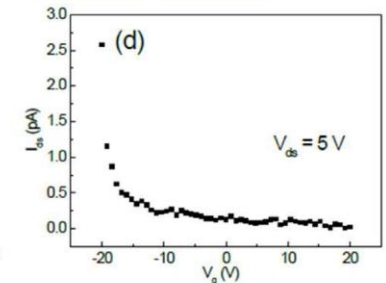
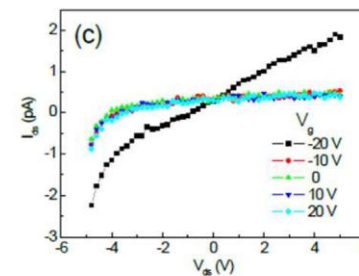
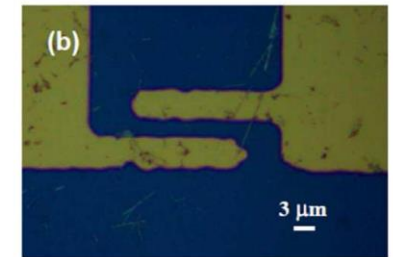
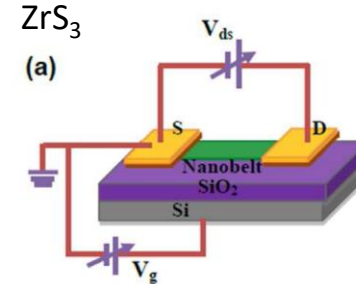
- High vacuum, low-leakage probing ideal for characterization of devices fabricated from air-sensitive 2D materials



MoS₂



ZrS₃

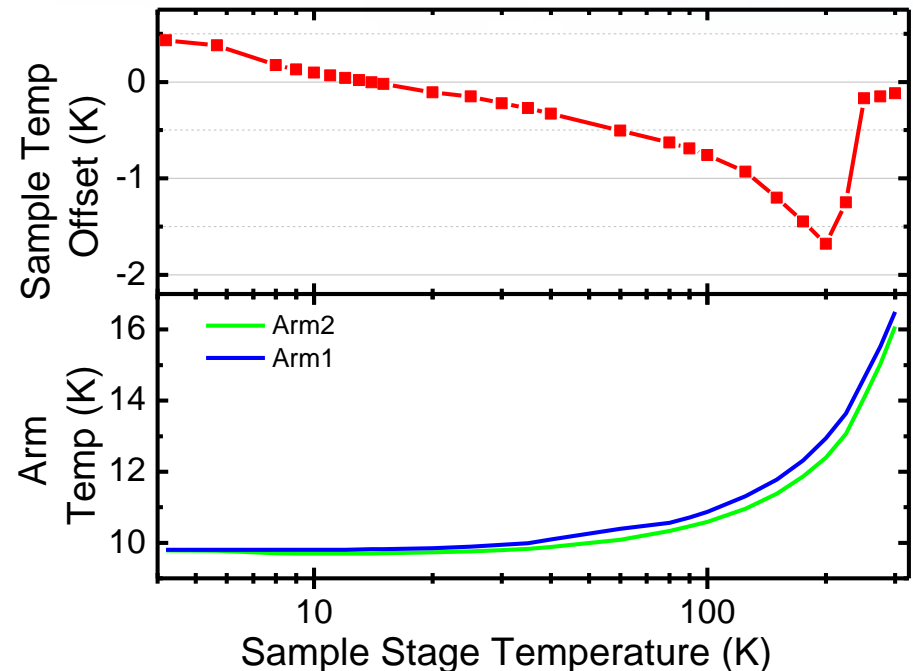
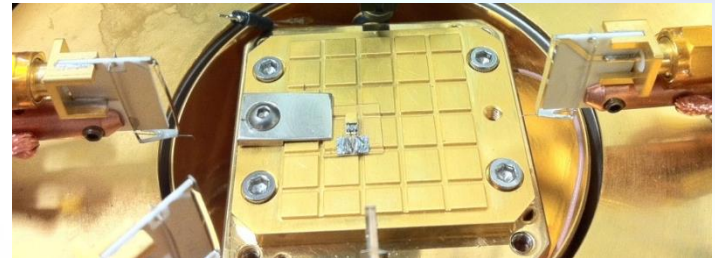


Cryogenic transport (I-V) measurements

Thermal considerations

- Good device contact to thermal sample holder
- Thermally anchored probes
 - Minimizes heat load on device
 - Configurable for various operational conditions

CPX-VF probe station



Cryogenic transport (I-V) measurements

Recommended sample mounting

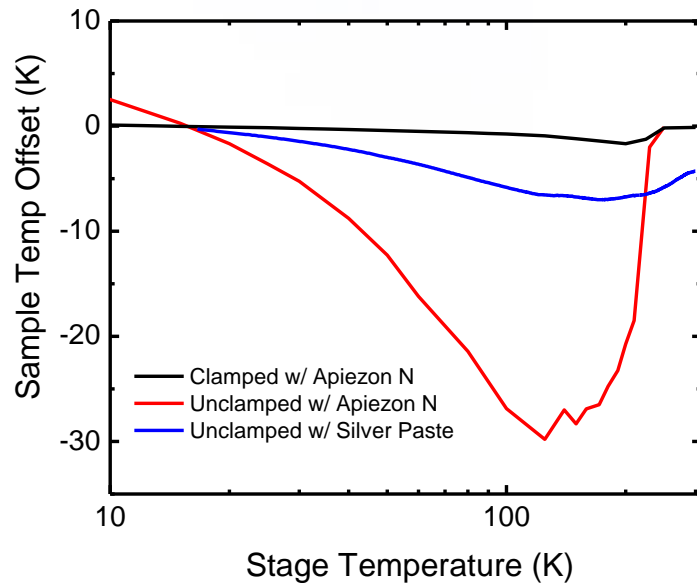
Method	Pro(s)	Con(s)
GE varnish (IMI 7031)	High thermal conductance	Long cure time, soaking sample and holder in aggressive solvent to remove
Vacuum grease & clamping	Quick sample exchange, good thermal conductance	Probe interference with clamps, wipe clean with Xylene
Silver paint & paste	Backside electrical contact, reasonable thermal conductance	When cleaning, mobile silver particles can short or damage devices
Carbon paste	Backside electrical contact, reasonable thermal conductance, can be used at higher temperatures	When cleaning, mobile carbon particles can short or damage devices
Cyanoacrylate (thin layer)	Quick cure, easy removal, suitable for small surface area	May not endure repeated thermal cycling

Not recommended for thermal reasons

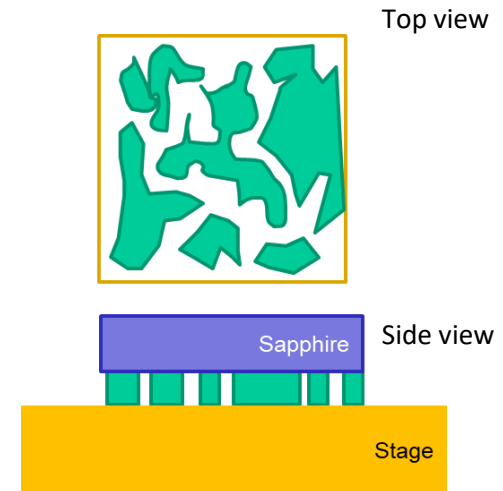
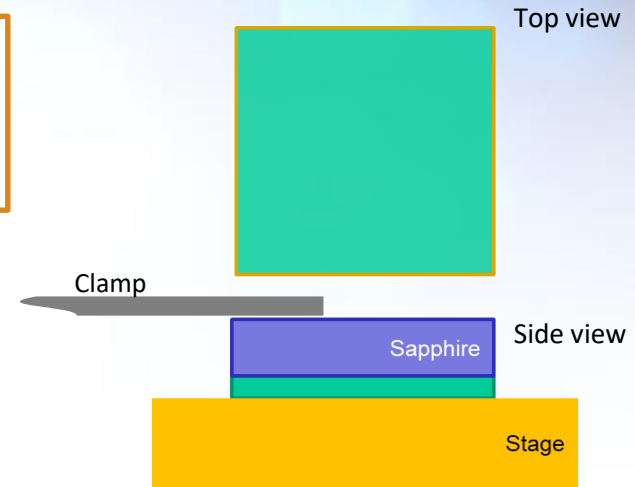
- Double-sided carbon tape
- Kapton tape
- Vacuum grease with no clamping

Cryogenic transport (I-V) measurements

If good mechanical clamping of substrate to sample stage is not possible, silver paste under sample offers better thermal contact than N-grease alone

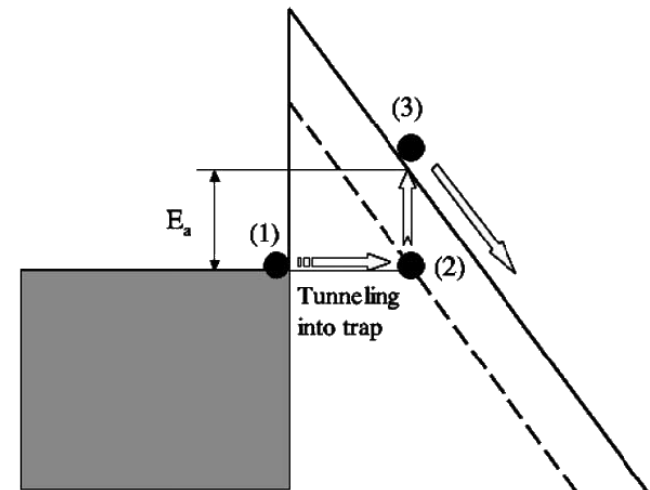
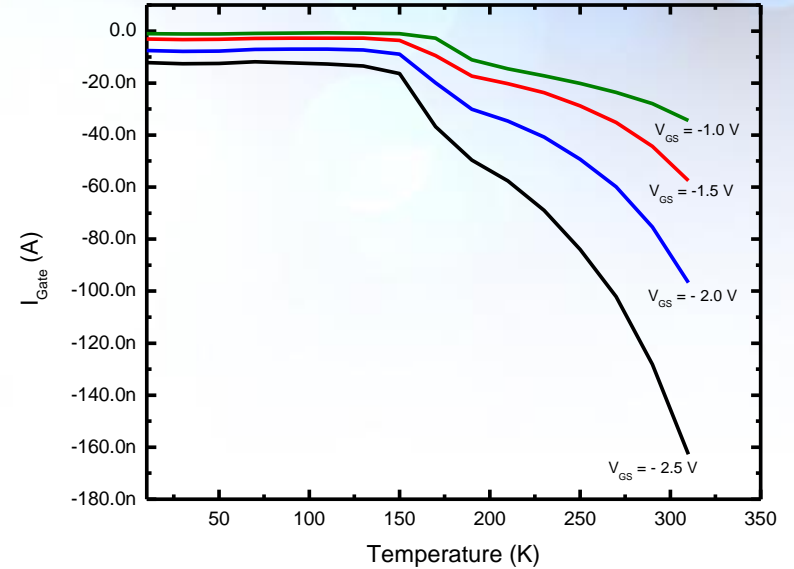
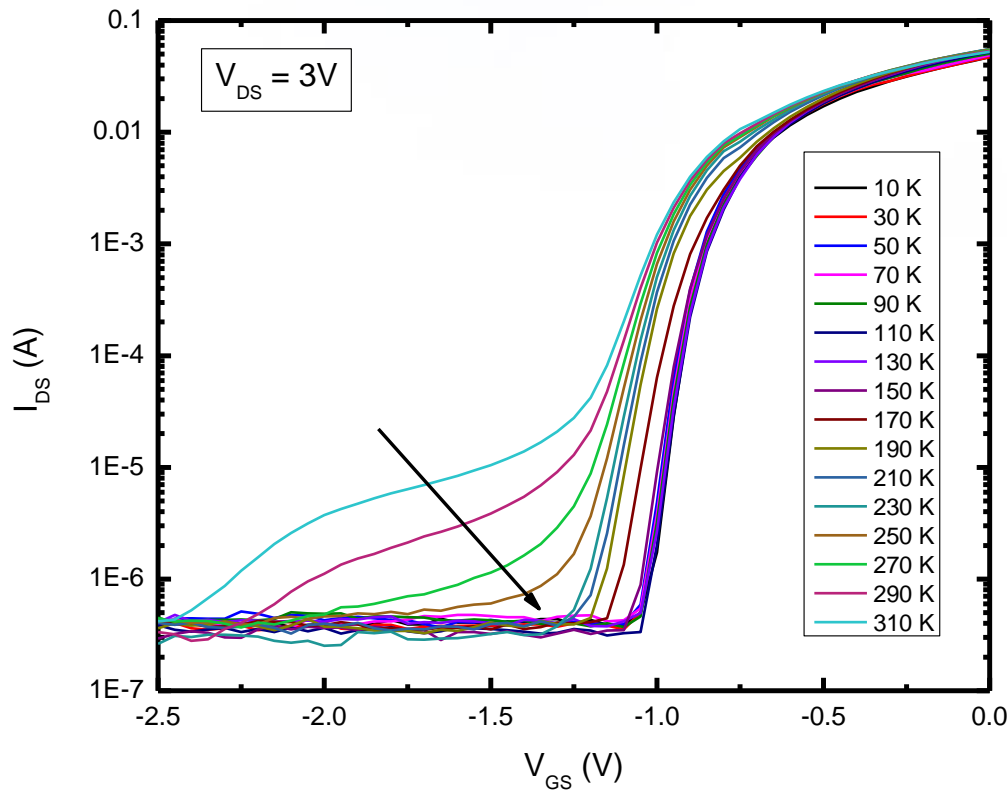


- Low temperature induced strain in polymer network is relieved by coarsening of Apiezon N film
- Coarsening results in spotty thermal transport to device substrate
- Applied clamping force changes thermodynamic landscape and reduces the onset film segmentation



Variable temperature pHEMT results

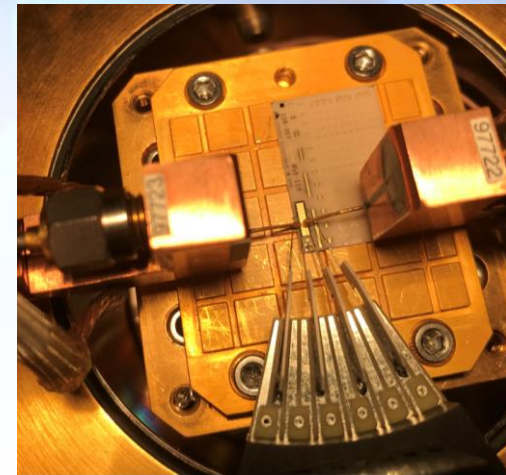
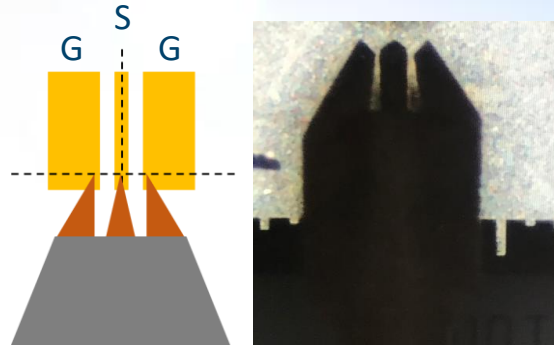
Temperature-dependent measurements revealed leakage mechanism



"Exploring Off-state Breakdown of GaAs pHEMTs at Cryogenic Temperatures"
Lake Shore Application Note, www.lakeshore.com

Microwave probing

- Cabling and cryogenic probes for:
 - DC to 40 GHz
 - DC to 67 GHz
- Calibration substrates

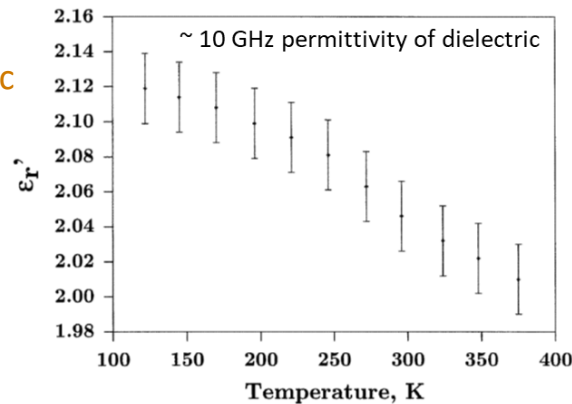
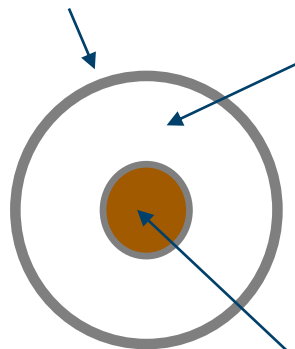


Recommend mounting calibration substrate on sample stage and executing calibration at every temperature of interest

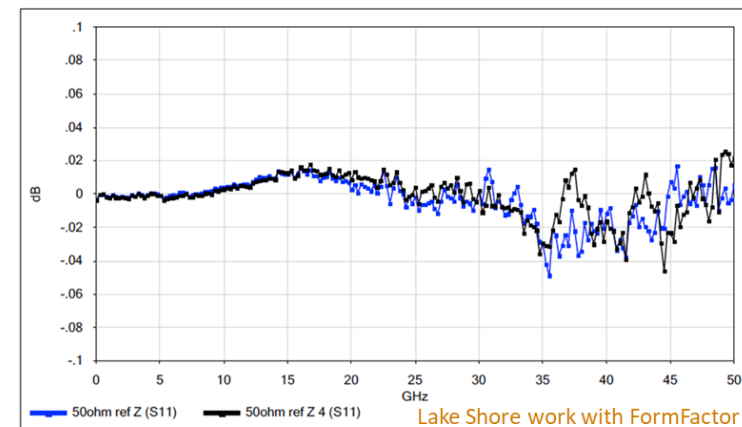
Outer conductor

Dielectric

Inner conductor

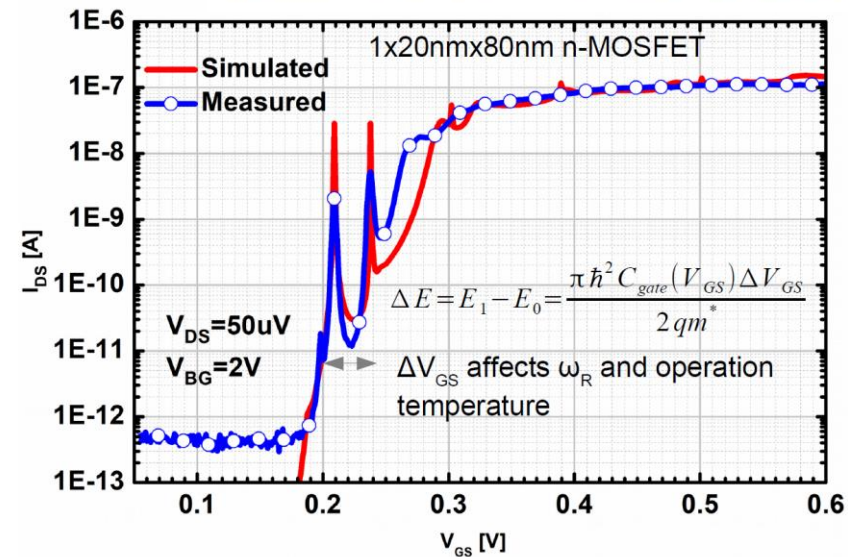
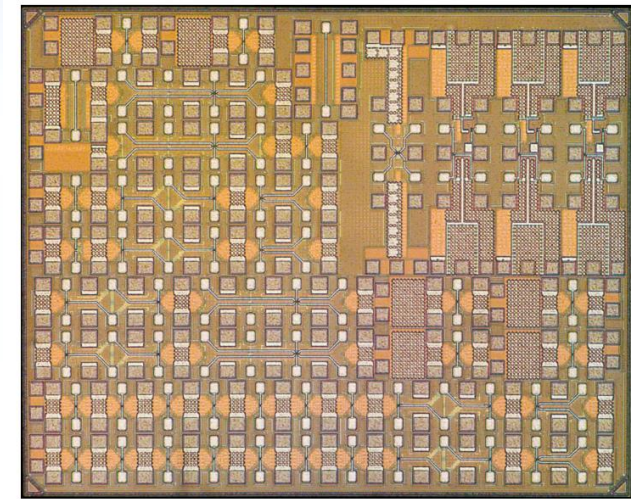
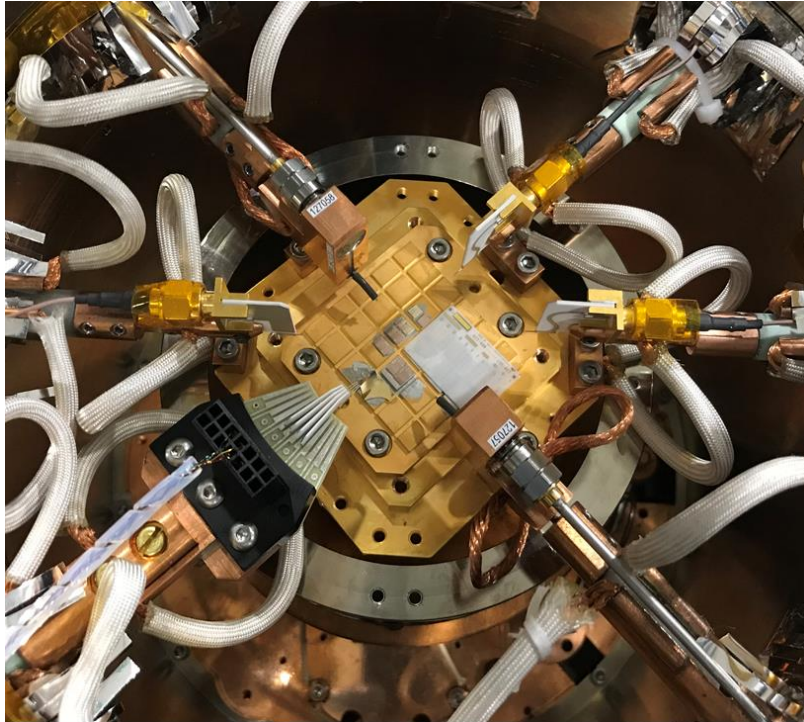


4 K open measurement following wafer-level calibration — ~2 hours between curves



Monolithic quantum computing ICs

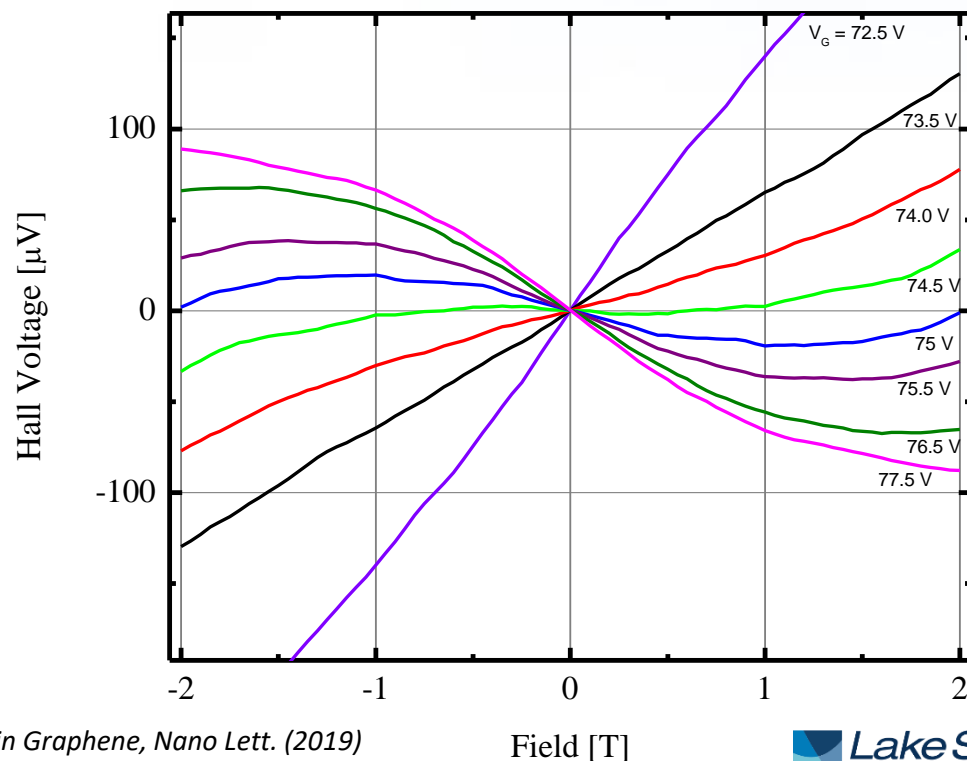
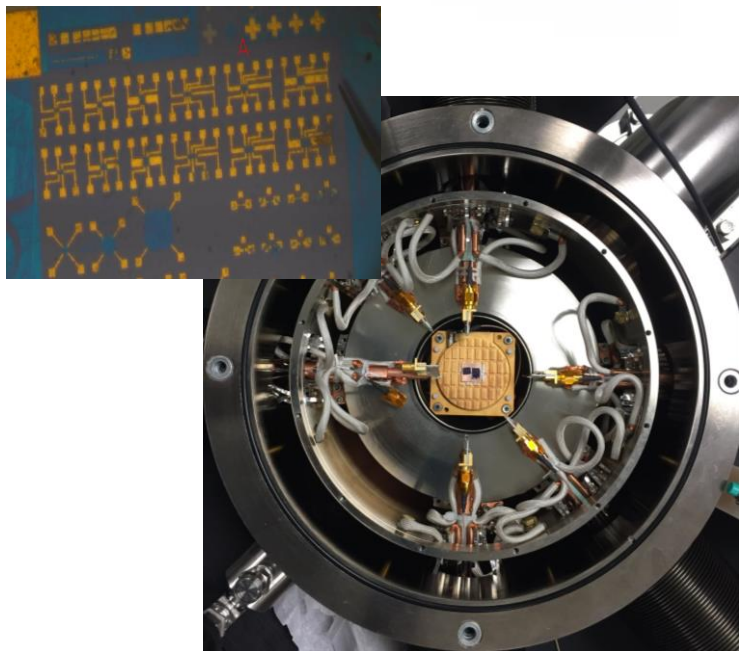
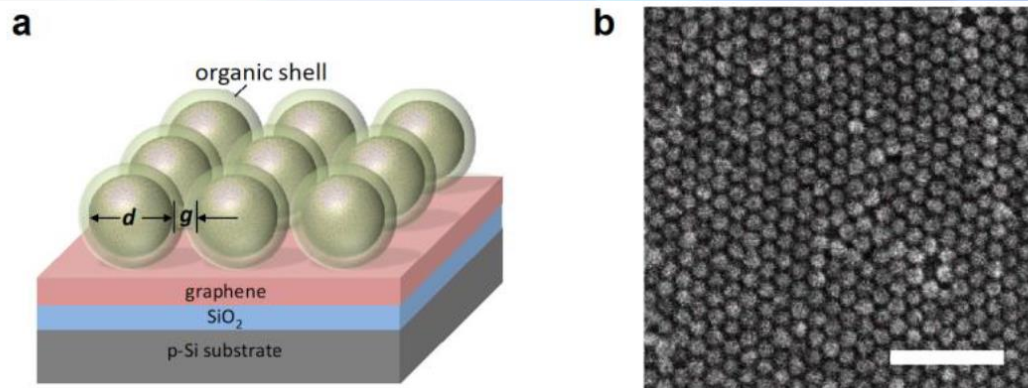
- 2 K sample stage temperature
- Integration of 67 GHz microwave probe, low-leakage DC transport measurements & multiple DC bias pins for gating
- Future: with magnetic field & 140 GHz probing



“Cryogenic Characterization of 22-nm FDSOI CMOS Technology for Quantum Computing ICs”, IEEE EDL (2019).

Wafer-level, gated Hall effect measurement

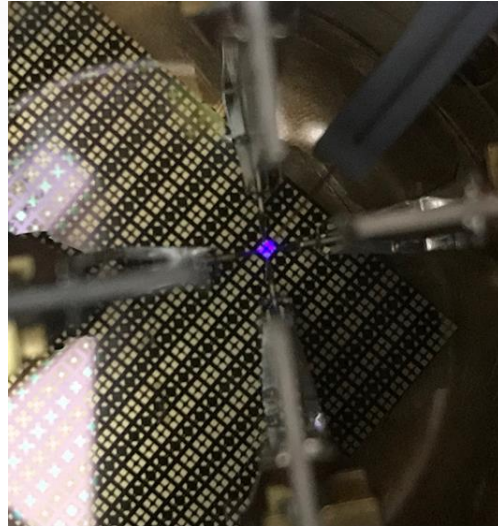
- Functionalized graphene
- 4- and 6-terminal Hall measurements
- Backside gating
- Proximity-induced ferromagnetism



Fiber optic solutions

Illumination

- UV-VIS, IR-VIS multimode
- Single mode & PM fiber
- Specials
 - Lensed
 - Solarization Resistant
 - Mid-IR



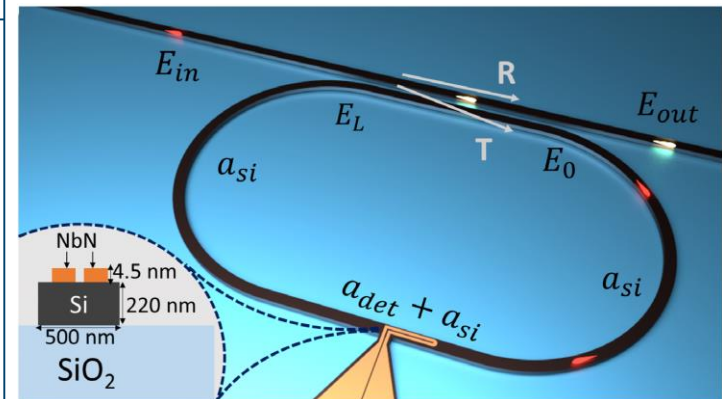
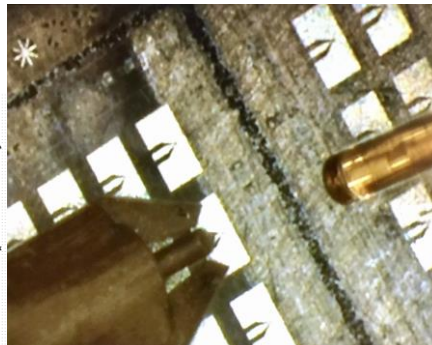
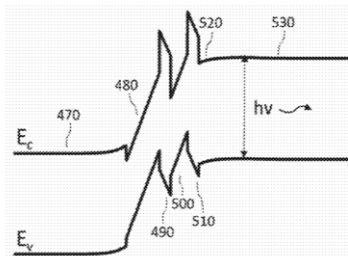
Integration



Collection

- UV-VIS, IR-VIS multimode

n-doped AlGaIn top contact
GaN top spacer (hole injector)
AlN barrier
GaN QW
AlN barrier
AlGaIn bottom spacer
n-doped AlGaIn bottom contact
AlN substrate



Summary

- Why use a probe station
- How:
 - Tailor the probes to the application
 - Use triaxial cabling for low current measurements
 - Mount your sample wafer appropriately
- What:
 - Transistor IV curves
 - Hall effect measurements (magnetic field)
 - Optical excitation and collection